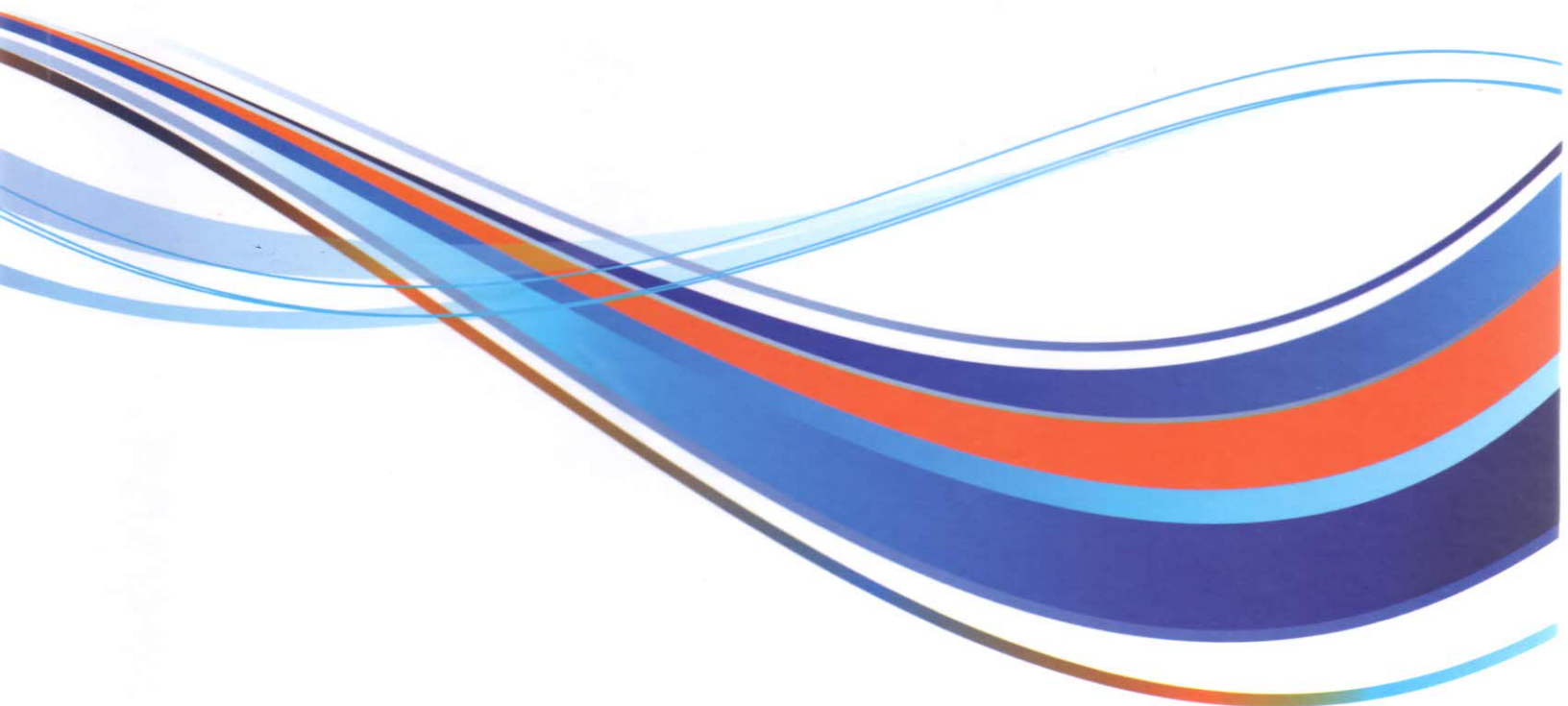


**In-house Qualified Processes  
for  
Hi-Rel Electronic  
&  
Microelectronic Fabrication,  
Assembly & Surface Treatment**



**Space Applications Centre, ISRO  
Ahmedabad**







तपन मिश्रा  
निदेशक  
Tapan Misra  
Director



भारत सरकार GOVERNMENT OF INDIA  
अंतरिक्ष विभाग DEPARTMENT OF SPACE

अंतरिक्ष उपयोग केंद्र  
SPACE APPLICATIONS CENTRE

अहमदाबाद AHMEDABAD - 380 015

(भारत) (INDIA)

दूरभाष PHONE : +91-79-26913344, 26928401

फैक्स / FAX : +91-79-26915843

ई-मेल E-mail : [director@sac.isro.gov.in](mailto:director@sac.isro.gov.in)



## MESSAGE

Space Applications Centre (SAC) is responsible for design and development of Satellite Communication (SATCOM), Navigation, Remote Sensing, Space Science and planetary exploration payloads using state-of-the-art technologies for the miniaturization, weight reduction, and reliable operations. Presently SAC is carrying out design, fabrication, assembly, testing and evaluation activities up to 60 GHz for Inter Satellite Link (ISL) and Temperature Sounding Unit (TSU). In future these capabilities are to be extended up to 220 GHz for Humidity Sounding Unit (HSU) etc.

In order to manufacture these state-of-the-art complex payloads, SAC have to qualify each and every process before using them for actual hardware

This document provides details of *in-house qualified processes* related to Hi-Rel electronic and microelectronic fabrication and assembly and surface treatment along with major specifications. I hope, this document would be very much useful to SAC/ISRO industrial partners to identify the processes of their interest for know-how transfer. SAC will be very happy to share the technology to Indian industry to take a step forward towards "Make in India Programme".

*Tapan Misra*

Place: Ahmedabad  
Date: 1 February 2016

(तपन मिश्रा)  
(Tapan Misra)



भारत सरकार  
अंतरिक्ष विभाग  
अंतरिक्ष उपयोग केंद्र  
अहमदाबाद - 380 015 (भारत)  
दूरभाष : +917926913395, 26913310  
फैक्स : +917926915815  
ई-मेल : rkasac@sac.isro.gov.in



Government of India  
Department of Space  
Space Applications Centre  
Ahmedabad - 380015 (India)  
Telephone: +917926913395, 26913310  
Fax : +917926915815  
E-Mail : rkasac@sac.isro.gov.in

राजकुमार अरोड़ा,  
उप.निदेशक, इएसएसए  
Rajkumar Arora  
Dy. Director, ESSA



### Message

An excellent document is made by Electronic Support Services Area (ESSA) team by compiling the in-house developed, qualified processes for *Hi-Rel electronic and microelectronic fabrication & assembly and surface treatment*. It also covers the salient features along with major specifications of respective qualified process.

This document will not only be useful for Space Applications Centre (SAC), ISRO community, but will be potential source for our industrial partners to identify the qualified process for manufacturing of space hardware and subsequently to acquire the knowhow from Technology Transfer & Industrial Interface Division (TTID).

Ahmedabad  
1<sup>st</sup> February 2016

राजकुमार अरोड़ा

(राजकुमार अरोड़ा)  
Rajkumar Arora

# Document Control Sheet

1	Report No. & Date	SAC/ESSA//TD/01 - February 2016
2	Title & Sub Title	Summary on in-house qualified processes for Hi-Rel Electronic and Microelectronic Fabrication, Assembly and Surface Treatment as on February 2016.
3	Type of Report	Technical
4	Pages	101
5	Authors	ESSA Team
6	Originating Unit	ESSA
7	Reviewed by	GD, MEG GD, EnTSG GH, EFMG
8	Approved by	DD, ESSA
9	Abstract	This document details out the Qualified Process for Fabrication of Micro electronics, SAW, PCBs fabrication, wiring and assembly, Surface Treatment & Thermal Control Coating for Space use.
10	Security Classification	Unclassified



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# Introduction

Space Applications Centre, Indian Space Research Organisation (ISRO) is responsible for design and development of various State of the art SATCOM, Navigation, Microwave and Optical remote sensing payloads for various societal and national applications. For reliable operation of payload, it has to meet very high reliability of the order of zero defects. In order to meet the assigned reliability every circuit, subsystem and payload have to undergo various reviews and they have to be fabricated and assembled using various qualified processes.

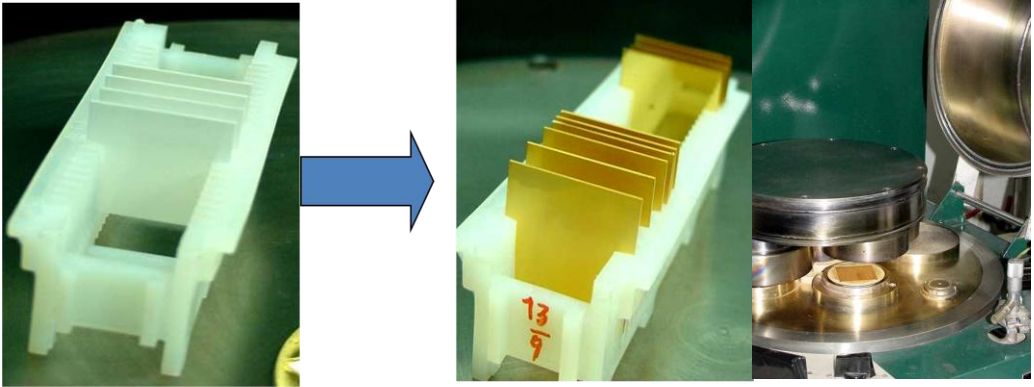
The respective subsystems and payloads undergo rigorous Test and Evaluation procedure. The qualified processes at Space Applications Centre (SAC) for fabrication and assembly of Microelectronics, SAW devices, PCBs, and Surface treatment on packages are summarized in this document titled as “In-house Qualified Processes for Hi-Rel Electronic and Microelectronic Fabrication, Assembly and Surface Treatment”. This document will be very much useful to Technology Transfer and Industry Interface Division for technology transfer to Indian Industries to meet the enhanced Indian Space Research Organisation (ISRO) projects requirement.



1. Substrates processing (Cutting and Hole Drilling) on 10mil thick bare & metalized Alumina substrates using MS-20 Laser system	
<b>Salient Features</b>	<ul style="list-style-type: none"> <li>➤ Substrates cutting Hole drilling using MS-20 Laser system</li> <li>➤ Nd-YAG laser with 1.064 micron wave length</li> <li>➤ Beam diameter ~150 microns</li> <li>➤ Power level 0.5 W to 2.0W</li> <li>➤ Pulse repetition rate 1pulse/sec</li> </ul>
<b>Major Specifications of the Qualified Process</b>	<ul style="list-style-type: none"> <li>➤ 10 mil bare and metallized alumina substrates</li> <li>➤ Cutting Size 5 mm to 50 mm</li> <li>➤ Size tolerance <math>\pm 100</math> microns</li> <li>➤ Hole type circular and square</li> <li>➤ Hole sizes 1mm to 5mm</li> <li>➤ Location/positioning accuracy <math>\pm 50</math> microns</li> <li>➤ Circularity of hole <math>\pm 50</math> microns</li> <li>➤ Edge flatness <math>\pm 50</math> microns</li> </ul>


2. Cr-Au metallization on 25mil & 10mil thick Alumina substrates using RF Sputtering system	
<b>Salient Features</b>	<ul style="list-style-type: none"> <li>➤ Cr-Au metallization using Z-400 RF sputtering system</li> <li>➤ Diode configuration three platform and cathodes of 3" diameter target</li> <li>➤ 04 Nos. of 1 sq. inch substrates can be accommodate on each platform in single batch</li> <li>➤ Ultimate vacuum better than <math>1 \times 10^{-6}</math> Bar.</li> <li>➤ Process Vacuum: <math>1.0 \times 10^{-2}</math> to <math>4.0 \times 10^{-2}</math> Bar.</li> <li>➤ Argon flow with 2 bar pressure to achieve process vacuum</li> <li>➤ In situ cleaning by reverse sputtering</li> <li>➤ Power level: 1.2 kW to 1.6 kW</li> <li>➤ Plating: Duty cycle: <math>20\% \pm 5\%</math></li> <li>➤ Ontime: 2 ms, Off time: 8 ms</li> <li>➤ Average Current: 40mA to 60mA (with peak current 0.2A - 0.6A)</li> <li>➤ Bath temperature: 55 to 65 deg. C</li> <li>➤ pH value of bath: <math>4 \pm 0.5</math></li> </ul>



<p><b>Major Specifications of the Qualified Process</b></p>	<ul style="list-style-type: none"> <li>➤ Cr ~300 Angstrom</li> <li>➤ Au 0.5 to 0.7 microns by sputtering and followed by pulse plating to enhance the thickness</li> <li>➤ Total metal thickness 5.0 to 7 microns.</li> <li>➤ Uniformity of deposited film <math>\pm 10\%</math></li> <li>➤ Sheet Resistivity of metallization: <math>&lt; 0.006 \Omega/\square</math></li> </ul>
<p><b>Photograph</b></p>	

### 3. Cr-Au metallization on 25mil & 10mil thick Alumina substrates using Magnetron Sputtering system

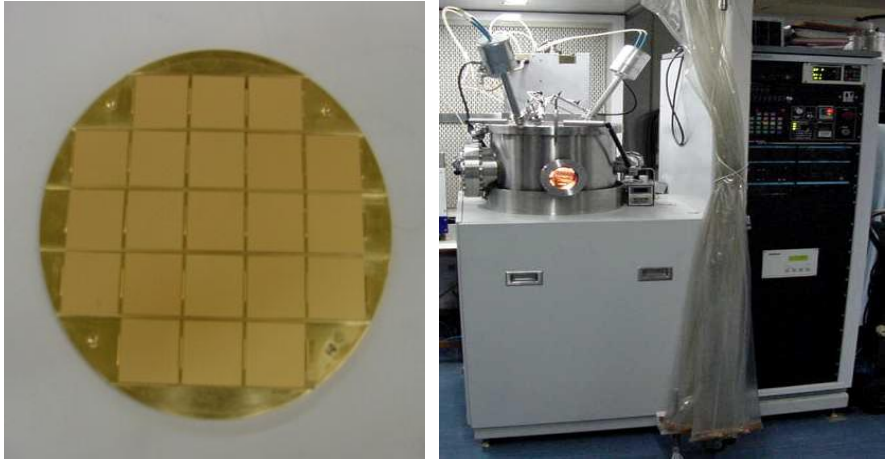
<p><b>Salient Features</b></p>	<ul style="list-style-type: none"> <li>➤ Cr-Au metallization using Denton Discovery-18 Magnetron sputtering system</li> <li>➤ Co focal arrangement of three cathodes on 3" target</li> <li>➤ 21 nos. of 1 sq.in substrates can be accommodate in single batch</li> <li>➤ Ultimate vacuum better than <math>1 \times 10^{-6}</math> Torr</li> <li>➤ Process vacuum: <math>5.0 \times 10^{-3}</math> to <math>2.0 \times 10^{-2}</math> Torr</li> <li>➤ Argon flow: 20 to 35 SCCM</li> <li>➤ In situ low energy ion cleaning</li> <li>➤ Rotation speed: ~10 rpm</li> <li>➤ Power level: 75W to 125W</li> <li>➤ Plating: Duty cycle: <math>20\% \pm 5\%</math></li> <li>➤ Ontime: 2 ms, Off time: 8 ms</li> <li>➤ Average Current: 40 to 60mA (with peak current 0.2 A - 0.6A)</li> <li>➤ Bath temperature: 55 to 65 deg. C</li> <li>➤ pH value of bath: <math>4 \pm 0.5</math></li> </ul>
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<p><b>Major Specifications of the Qualified Process</b></p>	<ul style="list-style-type: none"> <li>➤ Cr ~300 Angstrom</li> <li>➤ Au 0.5 to 0.7 microns by sputtering and followed by pulse plating to enhance the thickness</li> <li>➤ Total metal thickness 5.0 to 7 microns.</li> <li>➤ Uniformity of deposited film <math>\pm 10\%</math></li> <li>➤ Sheet Resistivity of metallization: <math>&lt; 0.006 \Omega/\square</math></li> </ul>
<p><b>Photograph</b></p>	

#### 4. Cr-Cu-Au metallization on 25mil thick Alumina substrates using Magnetron Sputtering system

<p><b>Salient Features</b></p>	<ul style="list-style-type: none"> <li>➤ Cr-Cu-Au metallization using Denton Discovery-18 Magnetron sputtering system</li> <li>➤ Co focal arrangement of three cathodes on 3" target</li> <li>➤ 21 nos. of 1 sq.in substrates can be accommodate in single batch</li> <li>➤ Ultimate vacuum better than <math>1 \times 10^{-6}</math> Torr</li> <li>➤ Process vacuum <math>5.0 \times 10^{-3}</math> to <math>2.0 \times 10^{-2}</math> Torr</li> <li>➤ Argon flow 20 to 35 SCCM</li> <li>➤ In situ low energy ion cleaning</li> <li>➤ Rotation speed ~10 rpm</li> <li>➤ Power level 75W to 125W</li> </ul>
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<b>Major Specifications of the Qualified Process</b>	<ul style="list-style-type: none"> <li>➤ Cr ~300 Angstrom</li> <li>➤ Cu 4-5 microns</li> <li>➤ Au 2 microns <math>\pm 10\%</math></li> <li>➤ Total metal thickness 5.8 to 7 microns.</li> <li>➤ Uniformity of deposited film <math>\pm 10\%</math></li> <li>Sheet Resistivity of the film: <math>&lt; 0.006 \Omega/\square</math></li> </ul>
<b>Photograph</b>	

## 5. NiCr/Al metallization on Quartz & LiNbO<sub>3</sub>

<b>Salient Features</b>	<ul style="list-style-type: none"> <li>➤ NiCr/Al metallization over Quartz &amp; LiNbO<sub>3</sub> required for Surface Acoustic Wave (SAW) devices, for Space craft Payload applications.</li> <li>➤ The required metallization was carried out by Vacuum evaporation process employing, NiCr resistively and e-beam gun for Al metallization.</li> </ul>
<b>Major Specifications of the Qualified Process</b>	<ul style="list-style-type: none"> <li>➤ Substrate material: Quartz and LiNbO<sub>3</sub></li> <li>➤ Substrate size: Piece part of 15mm X 30mm to 4"dia. Wafers</li> <li>➤ Metallization Thickness range: 1000Å to 2000Å</li> <li>➤ Thickness Tolerance: <math>\pm 10\%</math> of required metallization thickness</li> <li>➤ Uniformity of metalized film: <math>\pm 3\%</math> on 15mm X 30mm substrate size and <math>\pm 5\%</math> on 4" diameter wafers.</li> <li>➤ Sheet Resistivity of Al metallization: <math>&lt; 0.6 \Omega/\square</math></li> </ul>


**6. Alumina substrate dicing using High Speed Dicing (In-house and Vendors)**

<b>Salient Features</b>	<ul style="list-style-type: none"> <li>➤ Dicing of metalized and patterned alumina substrate for the various sizes ranging from 2.0X5.0 mm<sup>2</sup> to 12.7X25.4 mm<sup>2</sup> for Space craft Payload applications.</li> <li>➤ The required various size was carried out by High speed dicing</li> </ul>
<b>Major Specifications of the Qualified Process</b>	<ul style="list-style-type: none"> <li>➤ Substrate material: Alumina (Metalized and Patterned)</li> <li>➤ Substrate size: 2.0mmX5.0mm to 12.7mmX25.4mm</li> <li>➤ Thickness : 25 mil</li> <li>➤ Metallization : Two layer and Three layer</li> <li>➤ Edge Flatness: ±35microns</li> <li>➤ Cutting Accuracy: ± 100 microns</li> </ul>

**7. Substrates processing (cutting and hole drilling) on 25 mil thick bare & metalized Alumina substrates using MS-20 Laser system**

<b>Salient Features</b>	<ul style="list-style-type: none"> <li>➤ Substrates cutting Hole drilling using MS-20 Laser system</li> <li>➤ Nd-YAG laser with 1.064 micron wave length</li> <li>➤ Beam diameter: ~150 microns</li> <li>➤ Power level: 0.5 W to 2.0W</li> <li>➤ Pulse repetition rate: 1pulse/sec</li> </ul>
<b>Major Specifications of the Qualified Process</b>	<ul style="list-style-type: none"> <li>➤ 25 mil bare and metallized alumina substrates</li> <li>➤ Cutting Size 5 mm to 50 mm</li> <li>➤ Size tolerance ± 100 microns</li> <li>➤ Hole type circular and square</li> <li>➤ Hole sizes: 1mm to 5mm</li> <li>➤ Location/positioning accuracy: ± 50 microns</li> <li>➤ Circularity of hole: ±50 microns</li> <li>➤ Edge flatness: ±50 microns</li> </ul>

## 8. Cr-Au metallization on 10 mil thick Alumina substrates having 500 microns via hole using RF Sputtering System

<p><b>Salient Features</b></p>	<ul style="list-style-type: none"> <li>➤ Cr-Au metallization using Z-400 RF sputtering system</li> <li>➤ Diode configuration three platform and cathodes of 3" diameter target</li> <li>➤ 04 nos. of 1 sq. inch substrates can be accommodate on each platform in single batch</li> <li>➤ Ultimate vacuum better than <math>1 \times 10^{-6}</math> Bar.</li> <li>➤ Process vacuum: <math>1.0 \times 10^{-2}</math> to <math>4.0 \times 10^{-2}</math> Bar.</li> <li>➤ Argon flow with 2 bar pressure to achieve process vacuum</li> <li>➤ In situ cleaning by reverse sputtering</li> <li>➤ Power level: 1.2 kW to 1.6 kW</li> </ul> <p>Prior to plating of via hole substrates, abrasive cleaning is critical and required high skills.</p> <ul style="list-style-type: none"> <li>➤ Plating: Duty cycle: <math>20\% \pm 5\%</math></li> <li>➤ Ontime: 2 ms. Off time: 8 ms</li> <li>➤ Average current: 40 to 60 mA (with peak current 0.2 A to 0.6A)</li> <li>➤ Bath temperature: 55 to 65 deg. C</li> <li>➤ pH value of bath: <math>4 \pm 0.5</math></li> </ul>
<p><b>Major Specifications of the Qualified Process</b></p>	<ul style="list-style-type: none"> <li>➤ Hole diameter 500 microns</li> <li>➤ Cr ~300 Angstrom</li> <li>➤ Au 0.5 to 0.7 microns by sputtering and followed by pulse plating to enhance the thickness</li> <li>➤ Total metal thickness: 5.0 to 7 microns.</li> <li>➤ Uniformity of deposited film: <math>\pm 10\%</math></li> <li>➤ Contact resistance (ICR): <math>&lt; 0.002 \Omega</math></li> </ul>
<p><b>Photograph</b></p>	

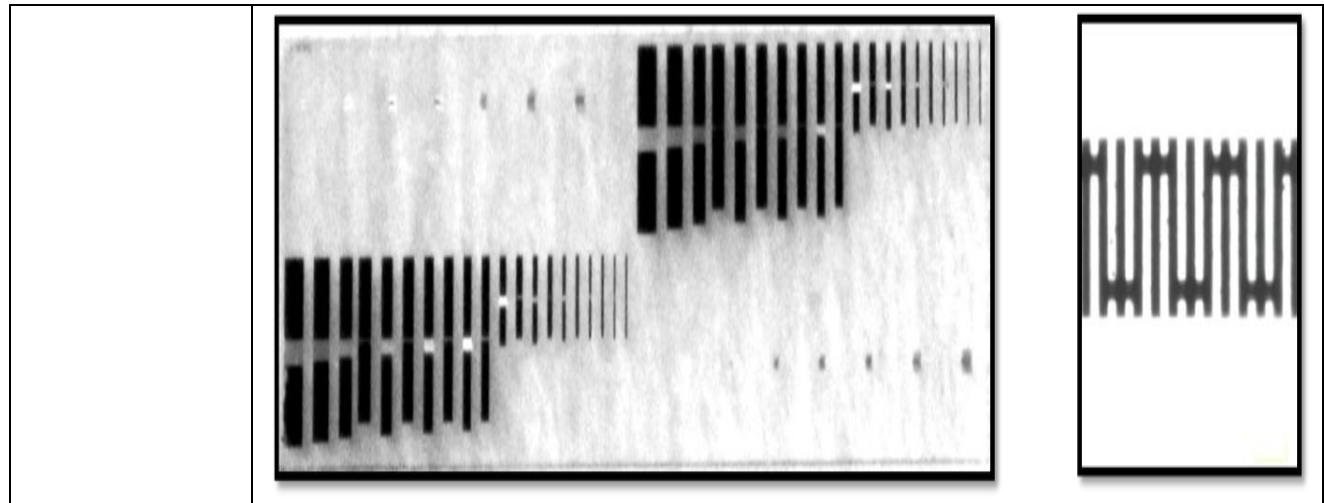


### 9. 500 microns hole drilling on 10 mil thick bare Alumina substrates using MS-20 Laser system for via hole metallization

<b>Salient Features</b>	<ul style="list-style-type: none"> <li>➤ Hole drilling using MS-20 Laser system</li> <li>➤ Nd-YAG laser with 1.064 micron wave length</li> <li>➤ Beam diameter: ~150 microns</li> <li>➤ Power level: 0.5 W to 2.0W</li> <li>➤ Pulse repetition rate: 1pulse/sec</li> </ul> <p>Burrs cleaning with diamond needle and U/S abrasive power cleaning requires high skills.</p>
<b>Major Specifications of the Qualified Process</b>	<ul style="list-style-type: none"> <li>➤ 10 mil bare alumina substrates</li> <li>➤ Total 11 holes in 12.7x12.7 mm square substrates.</li> <li>➤ Hole diameter 500 microns: <math>\pm 10\%</math></li> <li>➤ Location/positioning accuracy: <math>\pm 50</math> microns</li> <li>➤ Circularity of hole: <math>\pm 50</math> microns</li> <li>➤ Edge flatness: <math>\pm 50</math> microns</li> </ul>

### 10. Sub-micron Pattern Generation, $CD \geq 0.75\mu m$ , By Lift-off Process, On Quartz SAW Substrate


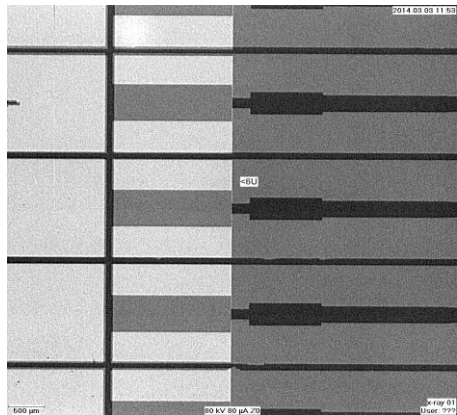

<b>Salient Features</b>	The process targets sub-micron pattern definition for high frequency SAW devices (typically for L Band frequencies). Unlike the older process based on wet chemical etching, it employs direct electron beam write and additive metal deposition.	
<b>Major Specifications of the Qualified Process</b>	<b>Parameters</b>	<b>Specifications</b>
	Wafer Material	Quartz
	Wafer Size / Thickness	3", 4" diameter / 0.5mm - 2mm
	Pattern	Equal Line / Space (IDT) patterns, CD down to $0.75\mu m$
	Lithography	E-Beam Lithography
	CD Control	$\pm 10\%$
	Evaporation	E-Beam Evaporation System
	Metallization Thickness Range	1000 - 3000Å°
	Metallization Thickness Control	$\pm 10\%$
	Metallization Thickness Uniformity	$\pm 5\%$ across the wafer
	Pattern Transfer	Lift-Off



### 11. Photolithography for SAW Pattern Generation. CD= 3 $\mu$ m, Tolerance = $\pm$ 20% or 3 $\mu$ m, whichever less

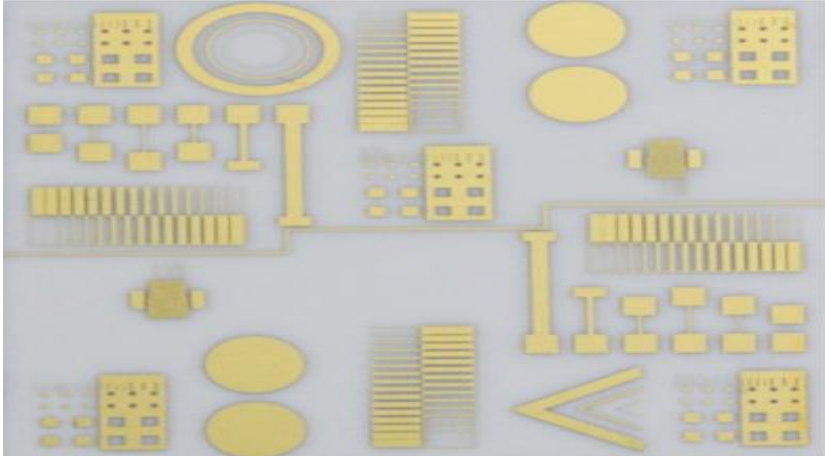
<b>Salient Features</b>	The process targets lithography for wider line dimension SAW devices and is based on wet chemical etching of NiCr and Al.	
<b>Major Specifications of the Qualified Process</b>	<b>Parameters</b>	<b>Specifications</b>
	Wafer Material	Quartz / LiNbO <sub>3</sub>
	Wafer Size / Thickness	3", 4" diameter / 0.5mm - 2mm
	Technique	Wet Chemical Etching
	Pattern	Equal Line / Space (IDT) patterns, CD down to 3 $\mu$ m
	Lithography	Photolithography
	CD Control	$\pm$ 20% or 3 $\mu$ m, whichever less
<b>Photograph</b>	Photolithography Qualification Sample 	

## 12. Double side Patterning of Cr-Au Metalized Substrates using Direct Write LASER (Phase 2)

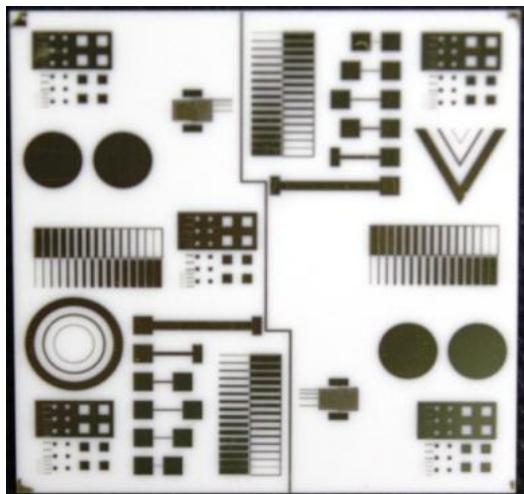
<b>Salient Features</b>	The process design and developed for front to back alignment (FTBA) with the alignment accuracy +/- 5 micron or better. Circuit critical (CD) dimensions targets 40 micron for high frequency (mm wave) applications. In this process, both sides of substrate patterned using mask-less LASER direct write technique by ensuring proper alignment between the patterns.	
<b>Major Specifications of the Qualified Process</b>	<b>Parameters</b>	<b>Specifications</b>
	Substrate Material	Alumina (99.6% or better)
	Dielectric Constant	9.8+/-0.1
	Substrate Size / Thickness	10 mm-25.4mm/ 254 micron (10 mil)
	Pattern	Any shape, line/gap patterns, CD down to 40µm
	Lithography	LASER direct write Lithography
	Technique	Back Side alignment
	CD Control	±10%
	Alignment Accuracy	+/- 5 micron
	Metallization Scheme	Cr-Au
	Metallisation Thickness Range	5-7 micron
	Metallisation Thickness Uniformity	±10% across the substrate
	Pattern Transfer	Wet etching
<b>Photograph</b>	 Top side pattern of mm wave circuit	 Front to back alignment (FTBA) measurement using X-ray technique
	 Bottom side pattern of mm wave circuit	



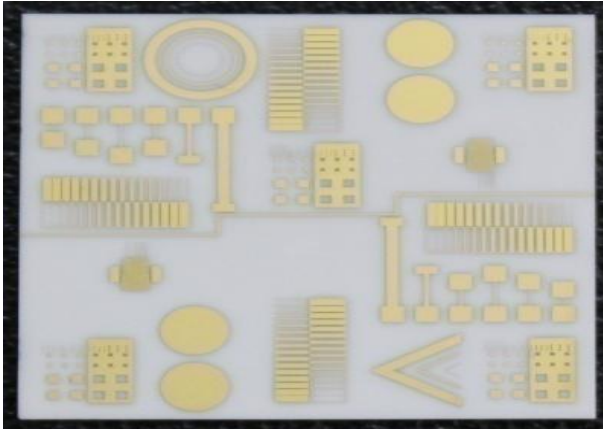
### 13. Photolithography and Circuit Engraving on In-house Cr-Cu-Au Metalized Substrates (Phase 2)

<b>Salient Features</b>	The process developed and parameters optimized for mask based photolithography and circuit engraving. Circuit critical (CD) dimensions targets 100 micron for ongoing communication, Navigation and Remote sensing payloads. In this process, chrome mask/ emulsion mask used to transfer the circuit image on to thin film. Wet chemical etching technique used to get film patterns on to substrate.	
<b>Major Specifications of the Qualified Process</b>	<b>Parameters</b>	<b>Specifications</b>
	Substrate Material	Alumina (99.6% or better)
	Make	In house metalized
	Dielectric Constant	9.8+/-0.1
	Substrate Size / Thickness	10mm-25.4mm/ 635 micron (25 mil)
	Pattern	Any shape, line/gap patterns, CD down to 100µm
	Lithography	Photolithography
	Mask	Chrome mask/ Emulsion mask
	CD Control	±10% or 25 micron whichever is less
	Metallization scheme	Cr-Cu-Au
	Metallisation Thickness Range	5-7 micron
	Metallisation Thickness Control	±10%
	Metallisation Thickness Uniformity	±10% across the Substrate
	Pattern Transfer	Wet etching
<b>Photograph</b>	<p>Phase-IV pattern used in in-house Cr-Cu-Au qualification</p> 	

#### 14. Photolithography and Circuit Engraving on M/s UHV metalized, Cr-Cu-Au Metalized Substrates (Phase 2)

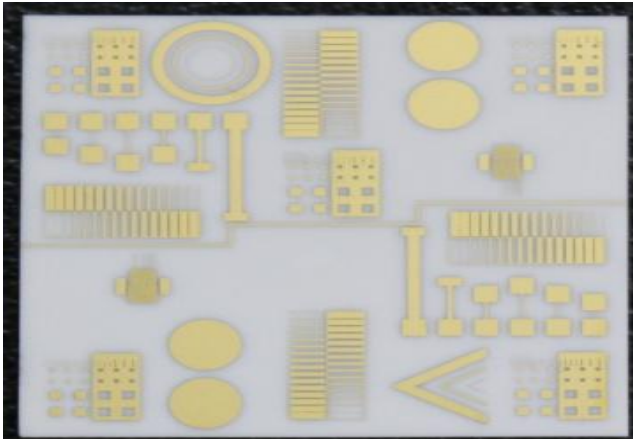
<b>Salient Features</b>	The process design and developed for mask based photolithography and circuit engraving. Circuit critical (CD) dimensions targets 100 micron for ongoing communication, Navigation and Remote sensing payloads. In this process, chrome mask/ emulsion mask used to transfer the circuit image on to thin film. Wet chemical etching technique used to get film patterns on to substrate.	
<b>Major Specifications of the Qualified Process</b>	<b>Parameters</b>	<b>Specifications</b>
	Substrate Material	Alumina (99.6% or better)
	Make	M/s UHV metalized
	Dielectric Constant	9.8+/-0.1
	Substrate Size / Thickness	10mm-25.4mm/ 635 micron (25 mil)
	Pattern	Any shape, line/gap patterns, CD down to 100µm
	Lithography	Photolithography
	Mask	Chrome mask/ Emulsion mask
	CD Control	±10% or 25 micron whichever is less
	Metallization scheme	Cr-Cu-Au
	Metallisation Thickness Range	5-7 micron
	Metallisation Thickness Control	±10%
	Metallisation Thickness Uniformity	±10% across the Substrate
	Pattern Transfer	Wet etching
<b>Photograph</b>	 <p>Phase-IV pattern used in M/s UHV Cr-Cu-Au qualification</p>	

### 15. Direct write LASER Lithography and Circuit Engraving on three layer metalized Alumina substrate

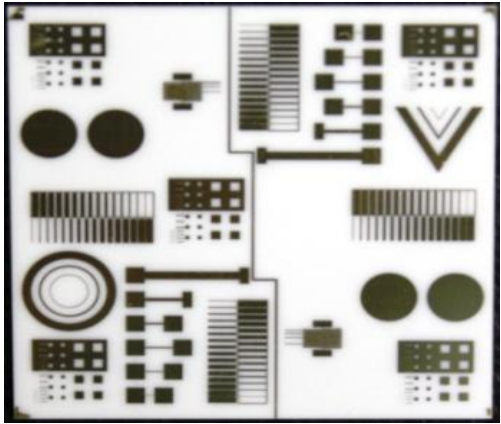
<b>Salient Features</b>	The process design and developed for mask-less direct write LASER lithography and circuit engraving. Circuit critical (CD) dimensions targets 100 micron on three layers (Cr-Cu-Au) for ongoing communication, Navigation and Remote sensing payloads. In this process, CAD data directly write using LASER beam on to resist coated substrate to get circuit image on to thin film. Wet etching technique used to get film patterns on to substrate.	
<b>Major Specifications of the Qualified Process</b>	<b>Parameters</b>	<b>Specifications</b>
	Substrate Material	Alumina (99.6% or better)
	Make	Supplied by MRC, TFT, Materion, USA
	Substrate Size / Thickness	10mm-25.4mm/ 635 micron (25 mil)
	Pattern	Any shape, line/gap patterns, CD down to 100µm
	Lithography	Direct write LASER
	Technique	Mask-less
	CD Control	±10% or 25 micron whichever is less
	Metallization scheme	Cr-Cu-Au
	Metallisation Thickness Range	5-7 micron
	Metallisation Thickness Control	±10%
	Metallisation Thickness Uniformity	±10% across the Substrate
	Pattern Transfer	Wet etching
<b>Photograph</b>	<p>Phase-IV pattern used in direct write LASER qualification for three layer metallized substrate</p> 	



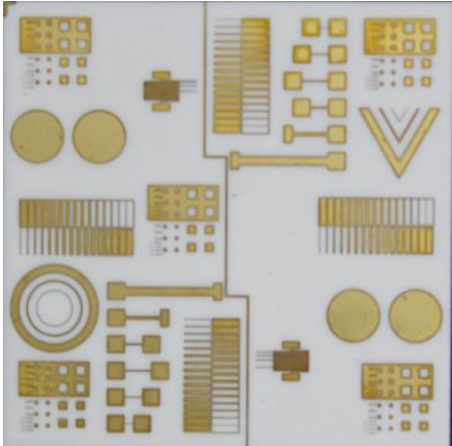
## 16. Direct write LASER lithography and circuit engraving on two layer metalized Alumina substrate

<b>Salient Features</b>	The process design and developed for mask-less direct write LASER lithography and circuit engraving. Circuit critical (CD) dimensions targets 40 micron on two layers (Cr-Au) for ongoing communication, Navigation and Remote sensing payloads. In this process, CAD data write in serial fashion on to resist coated substrate for transferring the circuit image on to thin film. Wet chemical etching technique used to get film patterns on to substrate.	
<b>Major Specifications of the Qualified Process</b>	<b>Parameters</b>	<b>Specifications</b>
	Substrate Material	Alumina (99.6% or better)
	Make	In-house metalized
	Substrate Size / Thickness	10mm-25.4mm/ 254 micron (10 mil)
	Pattern	Any shape, line/gap patterns, CD down to 40µm
	Lithography	Direct write LASER
	Technique	Mask-less
	CD Control	±10% or 25 micron whichever is less
	Metallization scheme	Cr-Au
	Metallisation Thickness Range	5-7 micron
	Metallisation Thickness Control	±10%
	Metallisation Thickness Uniformity	±10% across the Substrate
	Pattern Transfer	Wet etching
<b>Photograph</b>	<p>Phase-IV pattern used in direct write LASER qualification for In-house two layer metalized substrate</p> 	

### 17. Photo Lithography and Circuit Engraving on two layer metallized Alumina substrate

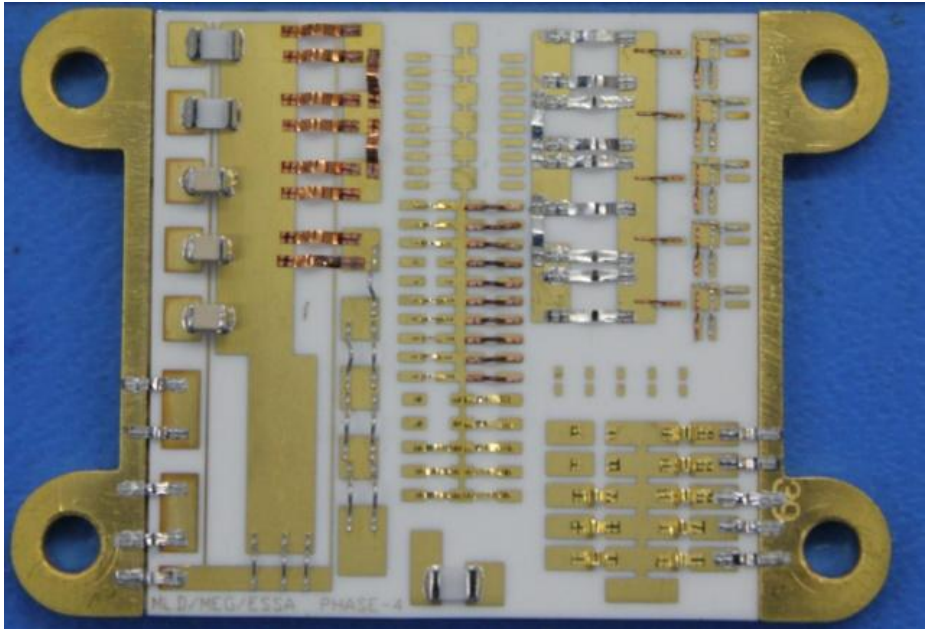
<b>Salient Features</b>	The process design and developed for mask based photolithography and circuit engraving. Circuit critical (CD) dimensions targets 100 micron for ongoing communication and Remote sensing payloads. In this process, emulsion mask used to transfer the circuit image on to thin film. Wet chemical etching technique used to get film patterns on to substrate.	
<b>Major Specifications of the Qualified Process</b>	<b>Parameters</b>	<b>Specifications</b>
	Substrate Material	Alumina (99.6% or better)
	Make	In-house metallized
	Substrate Size / Thickness	10mm-25.4mm/ 254 micron (10 mil)
	Pattern	Any shape, line/gap patterns, CD down to 40µm
	Lithography	Photolithography
	Mask	Emulsion mask prepared using photo-reduction technique
	CD Control	±10% or 25 micron whichever is less
	Metallization scheme	Cr-Au
	Metallisation Thickness Range	5-7 micron
	Metallisation Thickness Control	±10%
	Metallisation Thickness Uniformity	±10% across the Substrate
	Pattern Transfer	Wet etching
<b>Photograph</b>	<p>Phase-IV pattern used in Emulsion mask based photolithography for Cr-Au metalized substrate</p> 	

**18. Photo Lithography and Circuit Engraving on three layer metallized Alumina substrate**

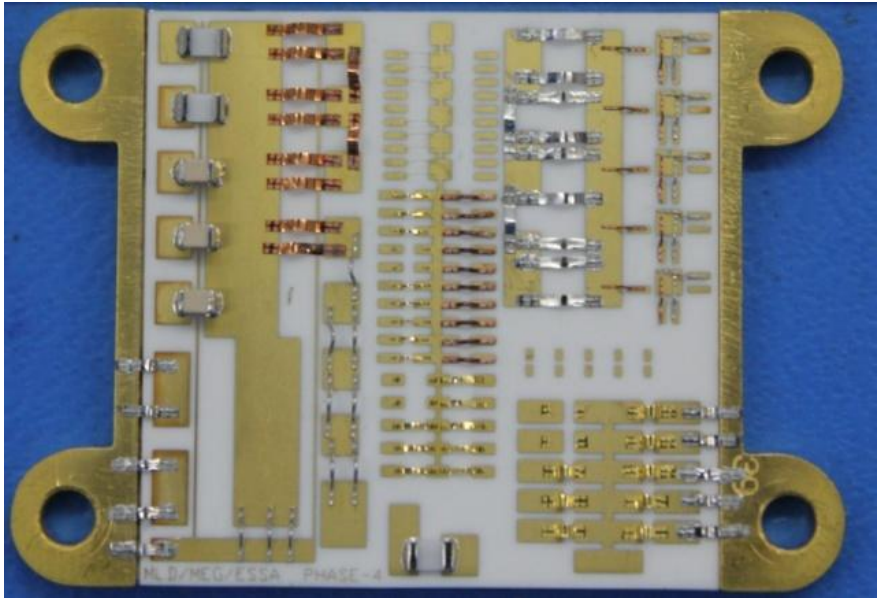
<b>Salient Features</b>	The process design and developed for emulsion mask based photolithography and circuit engraving. Circuit critical (CD) dimensions targets 100 micron for ongoing communication and Remote sensing payloads. In this process, emulsion mask (prepared using photo-reduction technique) used to transfer the circuit image on to thin film. Wet chemical etching technique used to get film patterns on to substrate.	
<b>Major Specifications of the Qualified Process</b>	<b>Parameters</b>	<b>Specifications</b>
	Substrate Material	Alumina (99.6% or better)
	Make	Supplied by MRC, TFT, Materion, USA
	Substrate Size / Thickness	10mm-25.4mm/ 635 micron (25 mil)
	Pattern	Any shape, line/gap patterns, CD down to 100µm
	Lithography	Photolithography
	Mask	Emulsion mask prepared using photo-reduction technique
	CD Control	±10% or 25 micron whichever is less
	Metallization scheme	Cr-Cu-Au
	Metallisation Thickness Range	5-7 micron
	Metallisation Thickness Control	±10%
	Metallisation Thickness Uniformity	±10% across the Substrate
	Pattern Transfer	Wet etching
<b>Photograph</b>	<p>Phase-IV pattern used in Emulsion mask based photolithography for Cr-Cu-Au metalized substrate</p> 	



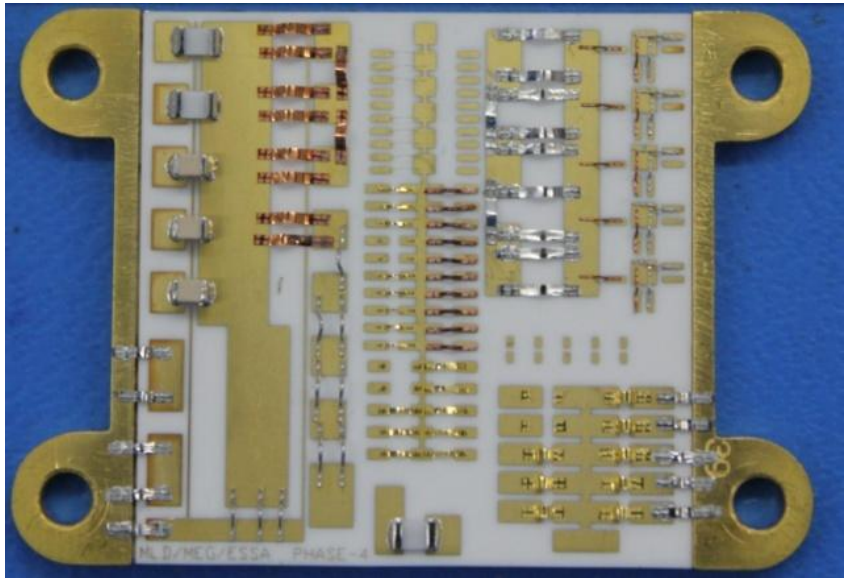
## 19. Assembly & Packaging of MIC on Alumina

<b>Introduction</b>	Three layers (Cr-Cu-Au) & Two layer (Cr-Au) metalized alumina substrates have been assembled & qualified prior to use in FM hardware samples were processed for MIC Assembly Processes for qualification testing.		
<b>Major Specifications of the Qualified Process</b>	<b>Salient Features</b>	<b>Technology</b>	<b>Feature Size</b>
	Substrate Type	Alumina	
	Substrate Size	1"X1", 25mil, 10mil	Three & two layer
	Attachment Process	Reflow process	Solder Preform Au/Sn 80/ 20
	Component Type & attachment Process	SMD, Reflow , Hot Gas & hand soldering process	Sn/Pb/Ag 62/36/2
	Gold Ribbon Bonding	Parallel Gap Bonding	20mil, 10mil, 5mil
	Gold Wire Bonding	Parallel Gap Bonding	1mil
	Epoxy (Conductive & Non Conductive)	Manual	H81 , H74
<b>Photograph</b>			

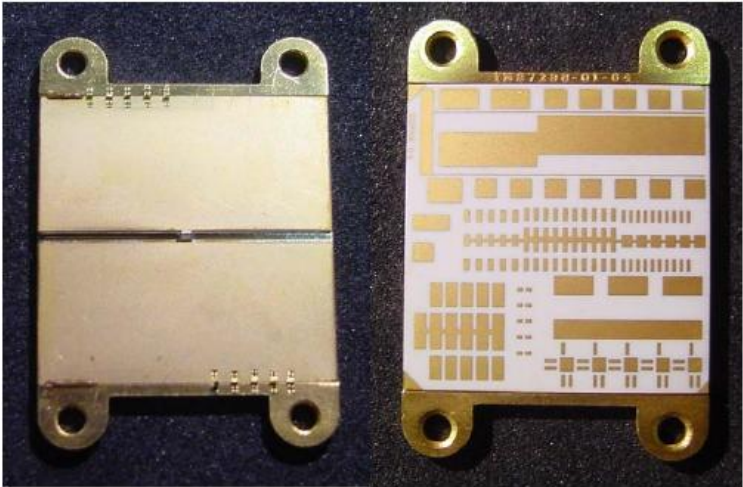
## 20. MIC Assembly Processes on Metallized Alumina Substrate of M/s UHV Sputtering

<b>Introduction</b>	Three layers (Cr-Cu-Au) metallized alumina substrates have been procured for the first time from M/s UHV Sputtering, U.S.A. by TSPD/MEG/ESSA. Hence, prior to use in FM hardware samples were processed for MIC Assembly Processes (as per Phase -IV, ISRO PAX-305) for qualification testing.		
<b>Major Specifications of the Qualified Process</b>	<b>Salient Features</b>	<b>Technology</b>	<b>Feature Size</b>
	Substrate Type	Alumina	
	Substrate Size	1"X1", 25mil	Three layer Cr-Cu-Au
	Attachment Process	Reflow process	Solder Preform Au/Sn 80/ 20
	Component Type & attachment Process	SMD, Reflow , Hot Gas & hand soldering process	Sn/Pb/Ag 62/36/2
	Gold Ribbon Bonding	Parallel Gap Bonding	20mil, 10mil, 5mil
	Gold Wire Bonding	Parallel Gap Bonding	1mil
	Epoxy (Conductive & Non Conductive)	Manual	H81 , H74
<b>Photograph</b>			

## 21. MIC Assembly Processes on In-house Metalized Alumina Substrate

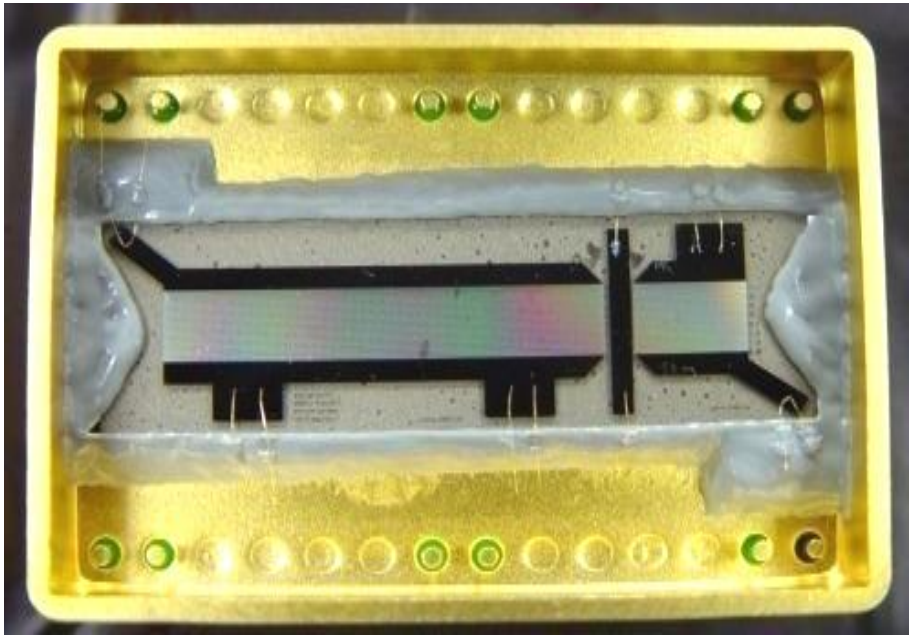
Major Specifications of the Qualified Process	Salient Feature	Technology	Feature Size
	Substrate Type	Alumina	
	Substrate Size	1"X1", 25mil	Three layer Cr-Cu-Au
	Attachment Process	Reflow process	Solder Preform Au/Sn 80/ 20
	Component Type & attachment Process	SMD, Reflow , Hot Gas & hand soldering process	Sn/Pb/Ag 62/36/2
	Gold Ribbon Bonding	Parallel Gap Bonding	20mil, 10mil, 5mil
	Gold Wire Bonding	Parallel Gap Bonding	1mil
	Epoxy (Conductive & Non Conductive)	Manual	H81 , H74
Photograph			

## 22. MIC Assembly Process on SILVAR Carrier Plate


Introduction	<p>SILVAR carrier plates are being planned to use in future Microwave Integrated Circuits (MICs) subsystem for high power applications. It provides “high thermal conductivity and thermal expansion coefficient matching with Alumina as well as GaAs. Since substrate &amp; bare die attachment, gold wire/ribbon bonding and gold epoxy application to gold-plated SILVAR carrier plate are new processes, it is essential to evaluate &amp; qualify the processes before starting FM fabrication.</p>		
Major Specifications of the Qualified Process	Salient Feature	Technology	Feature Size
	Substrate Type	Alumina	
	Substrate Size	1”X1”, ½”X1” 25mil	Three layer Cr-Cu-Au
	Attachment Process	Reflow process	Solder Preform Au/Sn 80/ 20
	MMIC Attachment	Reflow process	Solder Preform Au/Sn 80/ 20
	Component Type & attachment Process	SMD, Reflow , Hot Gas & hand soldering process	Sn/Pb/Ag 62/36/2
	Gold Ribbon Bonding	Parallel Gap Bonding	20mil, 10mil, 5mil
	Gold Wire Bonding	Parallel Gap Bonding	1mil
	Epoxy (Conductive & Non Conductive)	Manual	H81 , H74
Photograph			



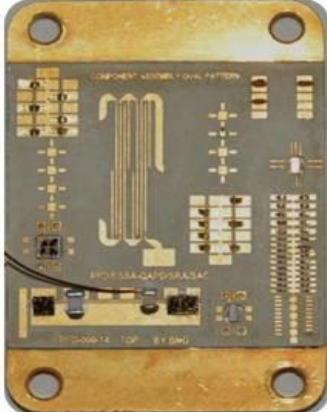
### 23. Assembly & Packaging of SAW devices

<b>Introduction</b>	Surface Acoustic Wave (SAW) is used for convert RF signal to SAW & vice versa. The SAW device is very brittle having aluminum metallization. The assembly of SAW substrate and gold wire bond between SAW & gold plated Package is qualified process for space Use.		
<b>Major Specifications of the Qualified Process</b>	<b>Salient Feature</b>	<b>Technology</b>	<b>Feature Size</b>
	Substrate Type	Quartz & $\text{LiNbO}_3$ and $\text{LiTaO}_3$	
	Package Size	1"x1" min & 1"x3" max, height 0.4" to 1"	
	Attachment Process	Epoxy Application	Conductive Epoxy RTV 1075
	Gold Wire Bonding	Parallel Gap Bonding	1mil
	RTV application	Manual	RTV3145
<b>Photograph</b>			


## 24. Kovar Hybrid Assembly Process using Alumina Substrate (Direct attach)

<b>Introduction</b>	<p>Hybrid circuits are used at various places in payload as an integration component or as a part of subsystem. The Hybrid is used after receivers to connect main and redundant receivers to the even and odd Input Multiplexers. The hybrid is fabricated using substrate attached on carrier plate &amp; carrier plate assembly in actual package. In this new process MIC substrate directly attached on gold plated Kovar package. With this process, size of whole circuit can be reduced and electrical performance can also be improved.</p>		
<b>Major Specifications of the Qualified Process</b>	<b>Salient Feature</b>	<b>Technology</b>	<b>Feature Size</b>
	Substrate Type	Alumina	
	Substrate Size	1"X ½" , 25mil & 10mil	Three layer Cr-Cu-Au
	Attachment Process	Reflow process	Solder Preform Au/Sn 80/ 20
	Component Type & attachment Process	SMD, Reflow , Hot Gas & hand soldering process	Sn/Pb/Ag 62/36/2
<b>Photograph</b>			

## 25. Duroid Assembly & Packaging of RT-Duroid 6002

<b>Introduction</b>	<p>Gold plated Duroid substrate are planned to be used in future subsystem for high power applications. The RF subsystems for communication &amp; earth observation payloads like GSAT-11, GISAT, etc. are to be realized using these laminates of various thickness &amp; sizes. The development of these types of payloads/subsystems requires following microwave assembly processes to be qualified on Duroid substrates</p> <ul style="list-style-type: none"> <li>a) Attachment of Duroid substrate to Kovar carrier plate</li> <li>b) Component mounting &amp; soldering on Duroid</li> <li>c) Gold Wire and ribbon bonding on Duroid</li> <li>d) Single layer multi-capacitor Chip mounting and wire bonding</li> <li>e) Gold epoxy application on Duroid</li> </ul>		
<b>Major Specifications of the Qualified Process</b>	<b>Salient Feature</b>	<b>Technology</b>	<b>Feature Size</b>
	Substrate Type	RT-Duroid 6002	
	Substrate Size	1"X1", 10mil	½ Oz Metallization
	Attachment Process	Reflow process	Sn/Pb/Ag 62/36/2
	MMIC Attachment	Manual	Silver Epoxy
	Component Type & attachment Process	SMD, Hot Gas & hand soldering process	Sn/Pb/Ag 62/36/2
	Gold Ribbon Bonding	Parallel Gap Bonding	20mil, 10mil, 5mil
	Gold Wire Bonding	Parallel Gap Bonding, wedge bonding	1mil
	Epoxy Gold & Silver	Manual	H81 , H21D
<b>Photograph</b>			

## 26. Duroid Assembly & Packaging of RT-Duroid 6010

Introduction	<p>Gold plated Duroid substrate are planned to be used in future subsystem for high power applications. The RF subsystems for communication &amp; earth observation payloads like GSAT-11, GISAT, etc. are to be realized using these laminates of various thickness &amp; sizes. The development of these types of payloads/sub systems requires following microwave assembly processes to be qualified on Duroid substrates</p> <ul style="list-style-type: none"> <li>a) Attachment of Duroid substrate to Kovar carrier plate</li> <li>b) Component mounting &amp; soldering on Duroid</li> <li>c) Gold Wire and ribbon bonding on Duroid</li> <li>d) Single layer multi-capacitor Chip mounting and wire bonding</li> <li>e) Gold epoxy application on Duroid</li> </ul>		
Major Specifications of the Qualified Process	Salient Feature	Technology	Feature Size
	Substrate Type	RT-Duroid 6010	
	Substrate Size	1"X1", 25mil	½ Oz metallization
	Attachment Process	Reflow process	Sn/Pb/Ag 62/36/2
	MMIC Attachment	Manual	Silver Epoxy
	Component Type & attachment Process	SMD, Hot Gas & hand soldering process	Sn/Pb/Ag 62/36/2
	Gold Ribbon Bonding	Parallel Gap Bonding	20mil, 10mil, 5mil
	Gold Wire Bonding	Parallel Gap Bonding, wedge bonding	1mil
	Epoxy Gold & Silver	Manual	H81 , H21D
Photograph			



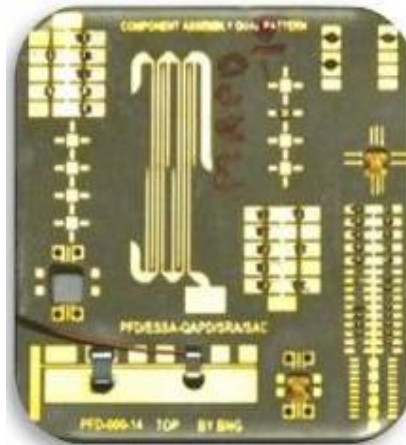
**27. Duroid Assembly & Packaging of RT-Duroid 6010 with cu back****Introduction**

Gold plated Duroid substrate are planned to be used in future subsystem for high power applications. The RF subsystems for communication & earth observation payloads like GSAT-11, GISAT, etc. are to be realized using these laminates of various thickness & sizes. The development of these types of payloads/sub systems requires following microwave assembly processes to be qualified on Duroid substrates

- a) Component mounting & soldering on Duroid
- b) Gold Wire and ribbon bonding on Duroid
- c) Single layer multi-capacitor Chip mounting and wire bonding
- d) Gold epoxy application on Duroid

**Major Specifications of the Qualified Process**

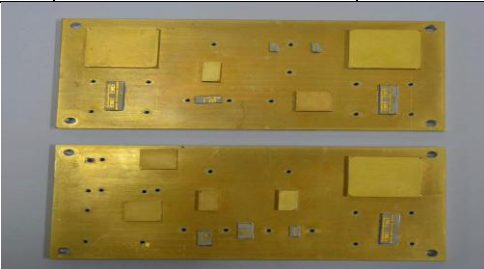
Salient Feature	Technology	Feature Size
Substrate Type	RT-Duroid 6010 with Cu Back	
Substrate Size	1"X1", 25mil	½ Oz metallization
Component Type & attachment Process	SMD, Hot Gas & hand soldering process	Sn/Pb/Ag 62/36/2
Gold Ribbon Bonding	Parallel Gap Bonding	20mil, 10mil, 5mil
Gold Wire Bonding	Parallel Gap Bonding,	1mil
Epoxy Gold	Manual	H81

**Photograph**

**29. Assembly Process on Double Side Patterned, 10 mil thick Alumina (Cr-Au) MIC**

<b>Introduction</b>	Assembly Process on Double Side Patterned, 10 mil Thick Two Layer (Cr-Au) Metallized Alumina Substrate (Cantilever Configuration) RF Transition used in SCATSAT-1 FESA LNA.		
<b>Major Specifications of the Qualified Process</b>	<b>Salient Feature</b>	<b>Technology</b>	<b>Feature Size</b>
	Substrate Type	Alumina	10mil thick
	Substrate Size	2.56mmx8.5mm	Two layer Cr-Au
	Attachment Process	Reflow process	Solder Preform Au/Sn 80/ 20
	Gold Ribbon Bonding	Parallel Gap Bonding	10mil, 5mil


**30. The epoxy-attach processes using Epotek H21D - Cu-back Duroid to Gold-plated Aluminium****31. The epoxy-attach processes using Epotek H21D - Substrate attached Kovar plate to Kovar.**

<b>Introduction</b>	The Ku & Ka band converter realization for GSAT-11 requires direct attachment of, 1) Cu-back Duroid on to gold-plated Aluminium packages & 2) Kovar Carrier (with substrate) on Gold-plated Kovar. In these processes, the attachments are to be carried out using Epotek H21D silver epoxy. Since these processes are being proposed for first time for space-use, it is essential to qualify prior to FM fabrication. The testing has been carried out on the samples, fabricated by MAPD/MEG/SRA.		
<b>Major Specifications of the Qualified Process</b>	<b>Salient Feature</b>	<b>Technology</b>	<b>Feature Size</b>
	Substrate Type	Cu-back Duroid	3.0 x 6.4 to 19.5 x 6.3
	Plate	Kovar	12.7 x 6.3 to 25.4 x 25.4
	Epoxy Silver	Manual	H21D
<b>Photograph</b>			

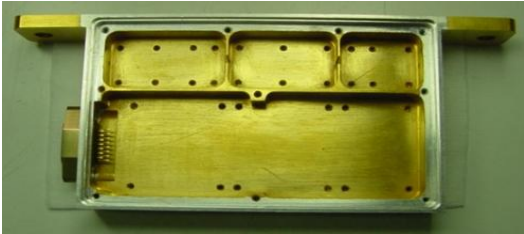
**32. Incremental Process Qualification using Solder & Epoxy**

<b>Introduction</b>	To meet project requirements in GSAT-16, it was planned to use HMC based control circuit for ALC DA. The PFT-substrate assembled at M/s Centum. While the post-optimization device assembly and wiring of this control circuit shall be completed at SAC. The HMC based control circuits are to be integrated in the ALC-DA package in-house and new processes are envisaged for the realization of control circuit of ALC DA are, Attachment of MMIC chip by silver epoxy, Cu-magnet wire soldering on HMC, Micro-D connector interconnections using Cu-magnet wire soldering, Component attachment using silver epoxy (Epotek H-21D).		
<b>Major Specifications of the Qualified Process</b>	<b>Salient Feature</b>	<b>Technology</b>	<b>Feature Size</b>
	Substrate Type	PFT	
	Cu-magnet wire solder	Hot Gas & hand soldering process	Sn/Pb/Ag 62/36/2
	Component attachment	Manual	Silver Epoxy
	Epoxy Silver	Manual	H81 , H21D


**33. Hermetic sealing process of Gold plated Al packages using laser welding of cover (Butt joint) and soldered DC & RF Feed-through**

<b>Introduction</b>	Hermetic sealing process of Gold plated Al Package using laser welding of cover (butt joint) qualified process for space Use.		
<b>Major Specifications of the Qualified Process</b>	<b>Salient Feature</b>	<b>Technology</b>	<b>Feature Size</b>
	Box Al6061, lid Al4047	Laser Hermetic sealing	Laser type Nd YAG wavelength 1064nm
	Box Size	125x45x25mm	-
	RF bead and DC feedthru attachment	Solder process	-
<b>Photograph</b>			

### 34. Hermetic sealing process of Micro D Connector with Gold plated Al packages using Laser Welding


<b>Introduction</b>	Hermetic sealing process of Micro D connector with Gold plated Al Package using laser welding qualified process for space Use.		
<b>Major Specifications of the Qualified Process</b>	<b>Salient Feature</b>	<b>Technology</b>	<b>Feature Size</b>
	Box Al6061, MicroD connector outershell Al4047	Laser Hermetic sealing	Laser type Nd YAG wavelength 1064nm
	Box Size	70x45x25mm	-
<b>Photograph</b>			

### 35. Hermetic sealing of Laser weldable RF connectors & DC feed through Hermetic with Al packages using Laser Welding

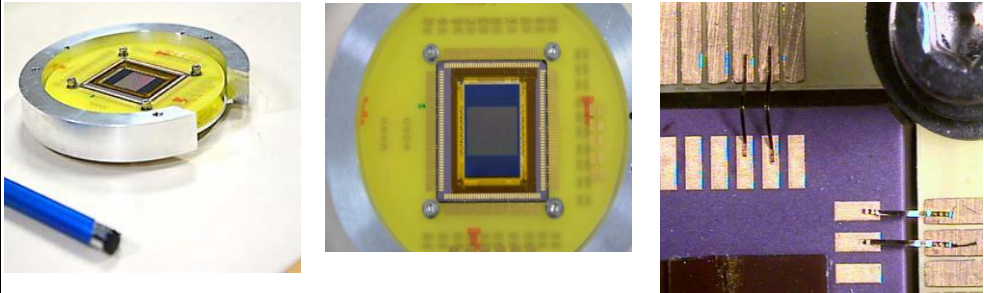
<b>Introduction</b>	Hermetic sealing process of Micro D connector with Gold plated Al Package using laser welding qualified process for space Use.		
<b>Major Specifications of the Qualified Process</b>	<b>Salient Feature</b>	<b>Technology</b>	<b>Feature Size</b>
	Box Al6061, laser weldable RF connector & DC feedthrough. Outer shell Al4047	Laser Hermetic sealing	Laser type Nd YAG wavelength 1064nm
	Box Size	45x45x25mm	-
<b>Photograph</b>			



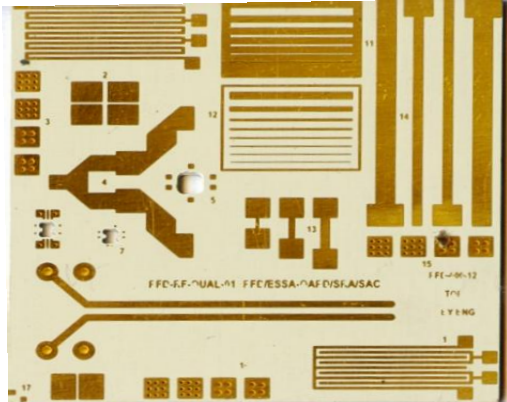
**36. Laser welding of cover by Lap fillet type joint**

<b>Introduction</b>	Hermetic sealing process of Micro D connector with Gold plated Al Package using laser welding qualified process for space use.		
<b>Major Specifications of the Qualified Process</b>	<b>Salient Feature</b>	<b>Technology</b>	<b>Feature Size</b>
	Box Al6061, lid Al4047	Laser Hermetic sealing	Laser type Nd YAG wavelength 1064nm
	Box Size	45x45x25mm	-
<b>Photograph</b>			

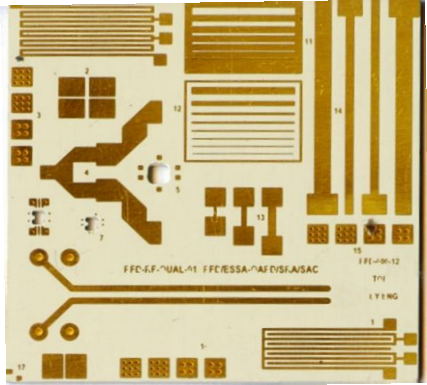
**37. Gold plated FR-4 PCB, 5mil Ribbon Bonding Process for Detector cleared for ASTROSAT UVIT only**

<b>Introduction</b>	This is with reference to meeting held on in May, 2014 for evaluation of gold ribbon bonding for making interconnection of CIS2051 Detector to gold-plated FR4 PCBs. An exercise has been carried out with one detector bonded on metal plate and interconnections are made through 5-mil ribbon bonds.		
<b>Major Specifications of the Qualified Process</b>	<b>Salient Feature</b>	<b>Technology</b>	<b>Feature Size</b>
	Substrate Type	Gold plated FR4 PCB	Supplied by PFD/ESSA
	Package with attached Detector	168-pin CIS2051 Detector (Electrically non-functional)	Assembled supplied by project.
	Interconnection	5mil ribbon bonding, parallel gap bonding	MAPD/ESSA
<b>Photograph</b>			

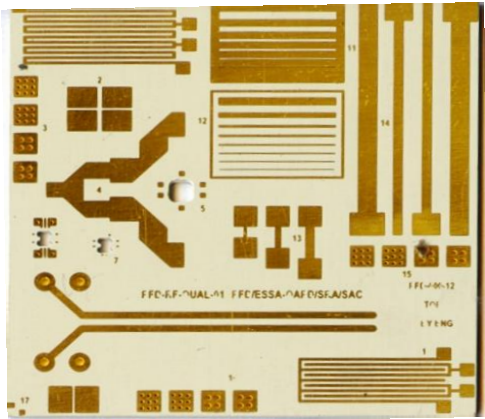
### 38. PTH and Pattern generation with Gold finished PCBs on RT Duroid 6002 having laminate thickness 10 mil & ¼ Oz basic Copper

<b>Salient Features</b>	Drilling of 10 mil thick RT Duroid 6010 laminate with ¼ Oz basic Cu is being done on high speed CNC drilling machine followed by the PTFE activation, PTH process and soft gold plating. After image transfer by using a negative photo film, gold and copper etching is carried out under the controlled condition to ensure minimum overhang and 130 micron lines and spacing can be achieved on a total minimum 50 micron copper thickness. Slot making and routing process is being carried out for the required size on CNC drilling machine.	
<b>Qualification test plan</b>	SAC/SRA/GEN/PQP/12.0/July 2013, Qualification Test plan for Gold plating / Solder Coating (using HAL) & pattern Generation Process of PCB fabrication with PTH on PTFE laminates.	
<b>Qualification Specifications</b>	<b>Description</b>	<b>Requirements</b>
	Laminate Type	RT-6002
	Laminate Thickness	10 mil
	Basic Copper thickness	¼ oz (8 µm)
	Type of Finish	Gold finish
	Track width / Spacing (min)	0.12 mm
	Gold plating Thickness (min)	2 µm ( 2 to 8 µm)
	Hole Size (min)	0.3mm
	Gold plating thickness in PTH	2 to 15 µm
	Slot size (min)	0.8 x 1.5 mm
<b>Photograph</b>		

### 39. PTH and Pattern generation with Gold finished PCBs on RT Duroid 6010 having laminate thickness 25 mil & ½ Oz basic Copper

<b>Salient Features</b>	Drilling of 25 mil thick RT Duroid 6010 laminate with ½ Oz basic Cu is being done on high speed CNC drilling machine followed by the PTFE activation, PTH process and soft gold plating. After image transfer by using a negative photo film, gold and copper etching is carried out under the controlled condition to ensure minimum overhang and 130 micron lines and spacing can be achieved on a total minimum 50 micron copper thickness. Slot making and routing process is being carried out for the required size on CNC drilling machine.	
<b>Qualification test plan</b>	SAC/SRA/GEN/PQP/12.0/July 2013, Qualification Test plan for Gold plating / Solder Coating (using HAL) & pattern Generation Process of PCB fabrication with PTH on PTFE laminates. PID No.: SAC\ESSA\EFMG\PFD\PID\01\MARCH, 2014	
<b>Qualification Specifications</b>	<b>Description</b>	<b>Requirements</b>
	Laminate Type	RT-6010
	Laminate Thickness	25 mil
	Basic Copper thickness	½ oz (17 µm)
	Type of Finish	Gold finish
	Track width / Spacing (min)	0.12 mm
	Gold plating Thickness (min)	2 µm ( 2 to 8 µm)
	Hole Size (min)	0.3mm
	Gold plating thickness in PTH	2 to 15 µm
	Slot size (min)	0.8 x 1.5 mm
<b>Photograph</b>		

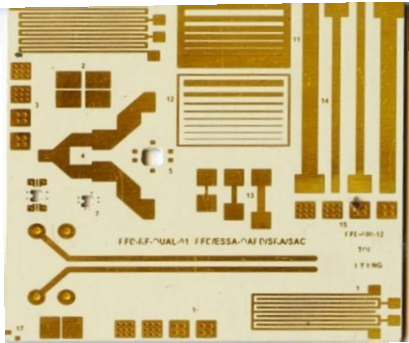
#### 40. PTH and Pattern generation with Gold finished PCBs on RT Duroid 6010 having laminate thickness 20 mil & ¼ Oz basic Copper

<b>Salient Features</b>	Drilling of 20 mil thick RT Duroid 6010 laminate with ¼ Oz basic Cu is being done on high speed CNC drilling machine followed by the PTFE activation, PTH process and soft gold plating. After image transfer by using a negative photo film, gold and copper etching is carried out under the controlled condition to ensure minimum overhang and 130 micron lines and spacing can be achieved on a total minimum 50 micron copper thickness. Slot making and routing process is being carried out for the required size on CNC drilling machine.	
<b>Qualification test plan</b>	SAC/SRA/GEN/PQP/12.0/July 2013, Qualification Test plan for Gold plating / Solder Coating (using HAL) & pattern Generation Process of PCB fabrication with PTH on PTFE laminates. PID No.: SAC\ESSA\EFMG\PFD\PID\01\MARCH, 2014	
<b>Qualification Specifications</b>	<b>Description</b>	<b>Requirements</b>
	Laminate Type	RT-6010
	Laminate Thickness	20 mil
	Basic Copper thickness	¼ oz (8 µm)
	Type of Finish	Gold finish
	Track width / Spacing (min)	0.12 mm
	Gold plating Thickness (min)	2 µm ( 2 to 8 µm)
	Hole Size (min)	0.3mm
	Gold plating thickness in PTH	2 to 15 µm
	Slot size (min)	0.8 x 1.5 mm
<b>Photograph</b>		

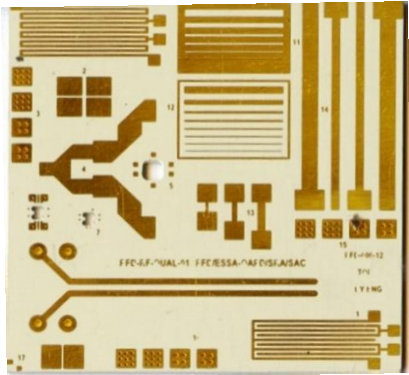




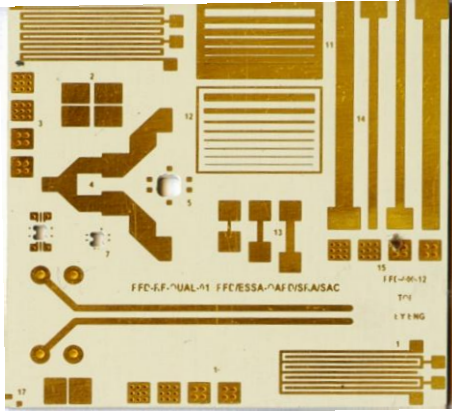
**42. PTH and Pattern generation with Gold finished PCBs on RT Duroid 6002 having laminate thickness 20 mil & ¼ Oz basic Copper and 1mm Cu backup**

<b>Salient Features</b>	Drilling of 20 mil thick RT Duroid 6002 laminate with ¼ Oz basic Cu & 1 mm thick copper backup is being done on high speed CNC drilling machine by using a pack drilling method followed by the PTFE activation, PTH process and soft gold plating. After image transfer by using a negative photo film, gold and copper etching is carried out under the controlled condition which ensures minimum overhang and 130 micron lines and spacing can be achieved on a total minimum 50 micron copper thickness. Slot making and routing process is being carried out for the required size on CNC drilling machine.	
<b>Qualification test plan</b>	SAC/SRA/GEN/PQP/12.0/July 2013, Qualification Test plan for Gold plating / Solder Coating (using HAL) & pattern Generation Process of PCB fabrication with PTH on PTFE laminates. PID No.: SAC\ESSA\EFMG\PFD\PID\02\JULY,2015	
<b>Qualification Specifications</b>	<b>Description</b>	<b>Requirements</b>
	Laminate Type	RT-6002 with 1mm copper backup
	Laminate Thickness	20 mil
	Basic Copper thickness	¼ oz (8 µm)
	Type of Finish	Gold finish
	Track width / Spacing (min)	0.12 mm
	Gold plating Thickness (min)	2 µm ( 2 to 8 µm)
	Hole Size (min)	0.5mm
	Gold plating thickness in PTH	2 to 15 µm
	Slot size (min)	0.8 x 1.5 mm
<b>Photograph</b>		

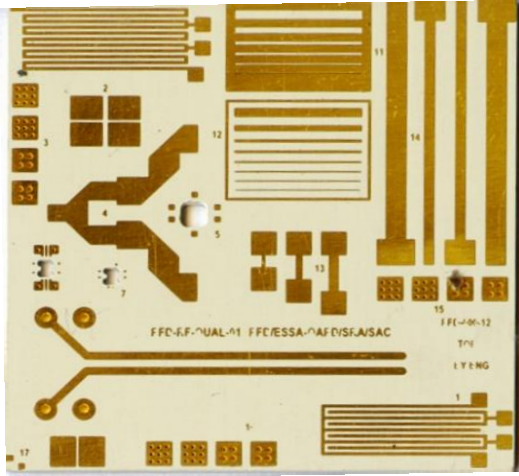
**43. PTH and Pattern generation with Gold finished PCBs on RT Duroid 6002 having laminate thickness 20 mil & ½ Oz basic Copper and 1mm Cu backup**

<b>Salient Features</b>	Drilling of 20 mil thick RT Duroid 6002 laminate with ½ Oz basic Cu & 1 mm thick copper backup is being done on high speed CNC drilling machine by using a pack drilling method followed by the PTFE activation, PTH process and soft gold plating. After image transfer by using a negative photo film, gold and copper etching is carried out under the controlled condition which ensures minimum overhang and 130 micron lines and spacing can be achieved on a total minimum 50 micron copper thickness. Slot making and routing process is being carried out for the required size on CNC drilling machine.	
<b>Qualification test plan</b>	SAC/SRA/GEN/PQP/12.0/July 2013, Qualification Test plan for Gold plating / Solder Coating (using HAL) & pattern Generation Process of PCB fabrication with PTH on PTFE laminates. PID No.: SAC\ESSA\EFMG\PFD\PID\02\JULY,2015	
<b>Qualification Specifications</b>	<b>Description</b>	<b>Requirements</b>
	Laminate Type	RT-6002 with 1mm copper backup
	Laminate Thickness	10 mil
	Basic Copper thickness	½ oz (17 µm)
	Type of Finish	Gold finish
	Track width / Spacing (min)	0.12 mm
	Gold plating Thickness (min)	2 µm ( 2 to 8 µm)
	Hole Size (min)	0.3mm
	Gold plating thickness in PTH	2 to 15 µm
	Slot size (min)	0.8 x 1.5 mm
<b>Photograph</b>		

#### 44. PTH and Pattern generation with Gold finished PCBs on CLTE XT having laminate thickness 20 mil & ½ Oz basic Copper

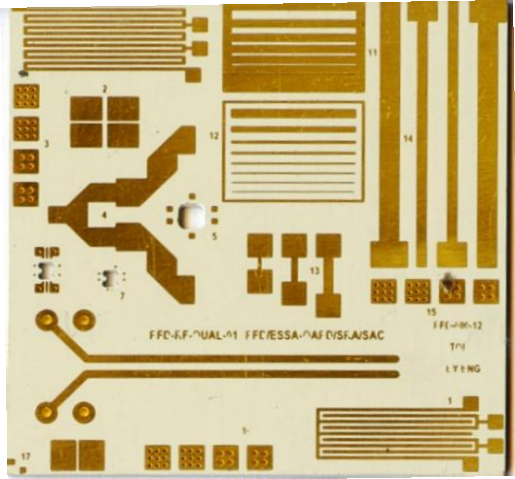
<b>Salient Features</b>	Drilling of 20 mil thick RT6002 laminate with ½ Oz basic Cu is being done on high speed CNC drilling machine followed by the PTFE activation, PTH process and soft gold plating. After image transfer by using a negative photo film, gold and copper etching is carried out under the controlled condition which ensures minimum overhang and 130 micron lines and spacing can be achieved on a total minimum 50 micron copper thickness. Slot making and routing process is being carried out for the required size on CNC drilling machine.	
<b>Qualification test plan</b>	SAC/SRA/GEN/PQP/12.0/July 2013, Qualification Test plan for Gold plating / Solder Coating (using HAL) & pattern Generation Process of PCB fabrication with PTH on PTFE laminates. PID No.: SAC\ESSA\EFMG\PFD\PID\01\MARCH, 2014	
<b>Qualification Specifications</b>	<b>Description</b>	<b>Requirements</b>
	Laminate Type	CLTE-XT
	Laminate Thickness	20 mil
	Basic Copper thickness	½ oz (17 µm)
	Type of Finish	Gold finish
	Track width / Spacing (min)	0.12 mm
	Gold plating Thickness (min)	2 µm ( 2 to 8 µm)
	Hole Size (min)	0.3mm
	Gold plating thickness in PTH	2 to 15 µm
	Slot size (min)	0.8 x 1.5 mm
<b>Photograph</b>		

#### 45. PTH and Pattern generation with Gold finished PCBs on TMM 6 having laminate thickness 25 mil & ½ Oz basic Copper

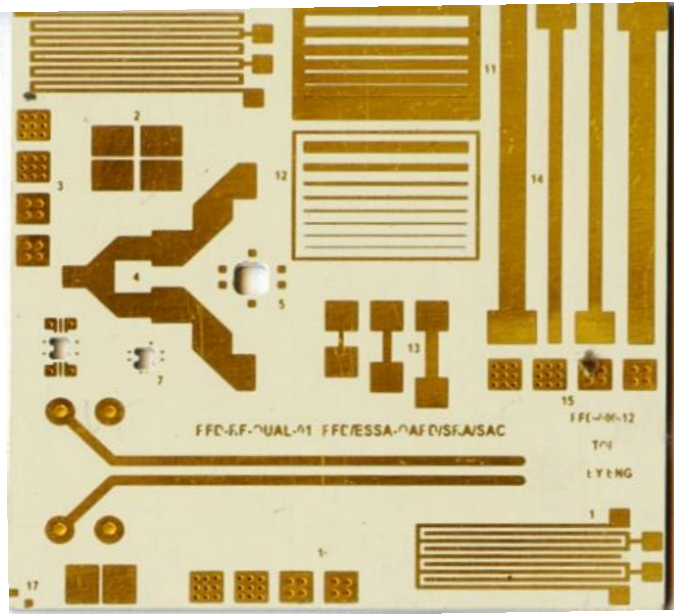
<b>Salient Features</b>	Drilling of 25 mil thick TMM 6 laminate with ½ Oz basic Cu is being done on high speed CNC drilling machine followed PTH process and soft gold plating. After image transfer by using a negative photo film, gold and copper etching is carried out under the controlled condition which ensures minimum overhang and 130 micron lines and spacing can be achieved on a total minimum 50 micron copper thickness. Slot making and routing process is being carried out for the required size on CNC drilling machine.	
<b>Qualification test plan</b>	SAC/SRA/GEN/PQP/12.0/July 2013, Qualification Test plan for Gold plating / Solder Coating (using HAL) & pattern Generation Process of PCB fabrication with PTH on PTFE laminates. PID No.: SAC\ESSA\EFMG\PFD\PID\01\JULY, 2015	
<b>Qualification Specifications</b>	<b>Description</b>	<b>Requirements</b>
	Laminate Type	TMM 6
	Laminate Thickness	25 mil
	Basic Copper thickness	½ oz (17 µm)
	Type of Finish	Gold finish
	Track width / Spacing (min)	0.12 mm
	Gold plating Thickness (min)	2 µm ( 2 to 8 µm)
	Hole Size (min)	0.3mm
	Gold plating thickness in PTH	2 to 15 µm
	Slot size (min)	0.8 x 1.5 mm
<b>Photograph</b>		



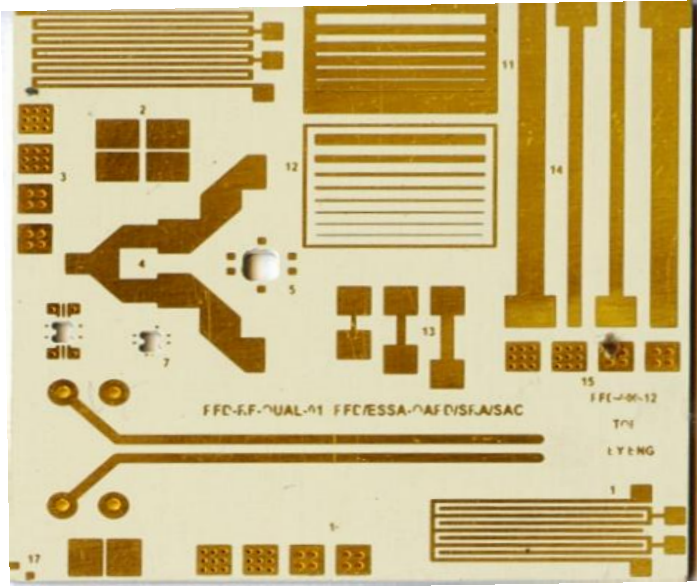
**46. PTH and Pattern generation with Gold finished PCBs on TMM10i having laminate thickness 15 mil & ½ Oz basic Copper**

<b>Salient Features</b>	Drilling of 15 mil thick TMM10i laminate with ½ Oz basic Cu is being done on high speed CNC drilling machine followed PTH process and soft gold plating. After image transfer by using a negative photo film, gold and copper etching is carried out under the controlled condition which ensures minimum overhang and 130 micron lines and spacing can be achieved on a total minimum 50 micron copper thickness. Slot making and routing process is being carried out for the required size on CNC drilling machine.	
<b>Qualification test plan</b>	SAC/SRA/GEN/PQP/12.0/July 2013, Qualification Test plan for Gold plating / Solder Coating (using HAL) & pattern Generation Process of PCB fabrication with PTH on PTFE laminates. PID No.: SAC\ESSA\EFMG\PFD\PID\01\JULY, 2015	
<b>Qualification Specifications</b>	<b>Description</b>	<b>Requirements</b>
	Laminate Type	TMM10i
	Laminate Thickness	15 mil
	Basic Copper thickness	½ oz (17 µm)
	Type of Finish	Gold finish
	Track width / Spacing (min)	0.12 mm
	Gold plating Thickness (min)	2 µm ( 2 to 8 µm)
	Hole Size (min)	0.3mm
	Gold plating thickness in PTH	2 to 15 µm
	Slot size (min)	0.8 x 1.5 mm
<b>Photograph</b>		

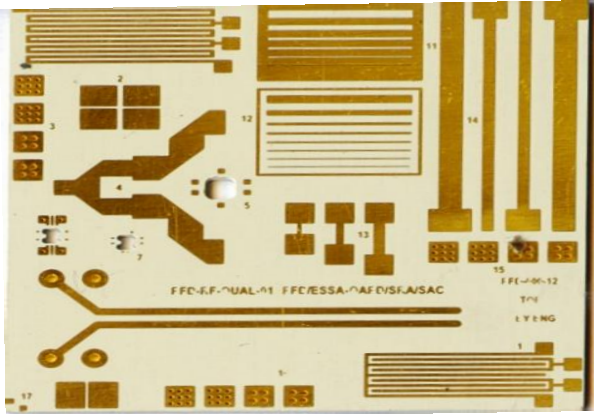
#### 47. NON PTH and Pattern generation with Gold finished PCBs on TMM10i having laminate thickness 50 mil & ½ Oz basic Copper

<b>Salient Features</b>	Drilling of 50 mil thick TMM10i laminate with ½ Oz basic Cu is being done on high speed CNC drilling machine followed by soft gold plating. After image transfer by using a negative photo film, gold and copper etching is carried out under the controlled condition which ensures minimum overhang and 100 micron lines and spacing. Routing process is being carried out for the required size on CNC drilling machine.	
<b>Qualification test plan</b>	SAC/SRA/GEN/PQP/12.0/July 2013, Qualification Test plan for Gold plating / Solder Coating (using HAL) & pattern Generation Process of PCB fabrication with PTH on PTFE laminates. PID No.: SAC\ESSA\EFMG\PFD\PID\01\JULY, 2015	
<b>Qualification Specifications</b>	<b>Description</b>	<b>Requirements</b>
	Laminate Type	TMM10i
	Laminate Thickness	50 mil
	Basic Copper thickness	½ oz (17 µm)
	Type of Finish	Gold finish
	Track width / Spacing (min)	0.100 mm
	Gold plating Thickness (min)	2 µm ( 2 to 8 µm)
<b>Photograph</b>		

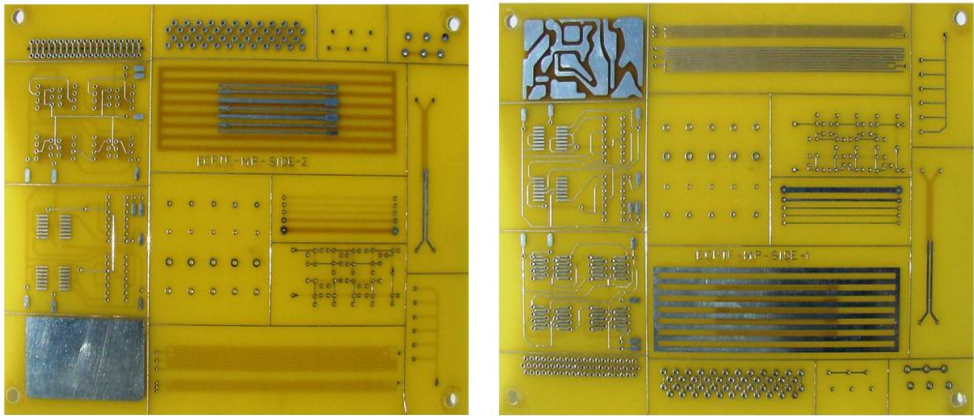
**48. NON PTH and Pattern generation with Gold finished PCBs on RT Duroid 6010 having laminate thickness 50 mil & ½ Oz basic Copper**

<b>Salient Features</b>	Drilling of 50 mil thick TMM10i laminate with ½ Oz basic Cu is being done on high speed CNC drilling machine followed by soft gold plating. After image transfer by using a negative photo film, gold and copper etching is carried out under the controlled condition which ensures minimum overhang and 100 micron lines and spacing. Routing process is being carried out for the required size on CNC drilling machine.	
<b>Qualification test plan</b>	SAC/SRA/GEN/PQP/12.0/July 2013, Qualification Test plan for Gold plating / Solder Coating (using HAL) & pattern Generation Process of PCB fabrication with PTH on PTFE laminates. PID No.: SAC\ESSA\EFMG\PFD\PID\01\MARCH, 2014	
<b>Qualification Specifications</b>	<b>Description</b>	<b>Requirements</b>
	Laminate Type	TMM10i
	Laminate Thickness	50 mil
	Basic Copper thickness	½ oz (17 µm)
	Type of Finish	Gold finish
	Track width / Spacing (min)	0.100 mm
	Gold plating Thickness (min)	2 µm ( 2 to 8 µm)
<b>Photograph</b>		

**49. NON PTH and Pattern generation with Gold finished PCBs on RT Duroid 5880 having laminate thickness 50 mil & ½ Oz basic Copper**

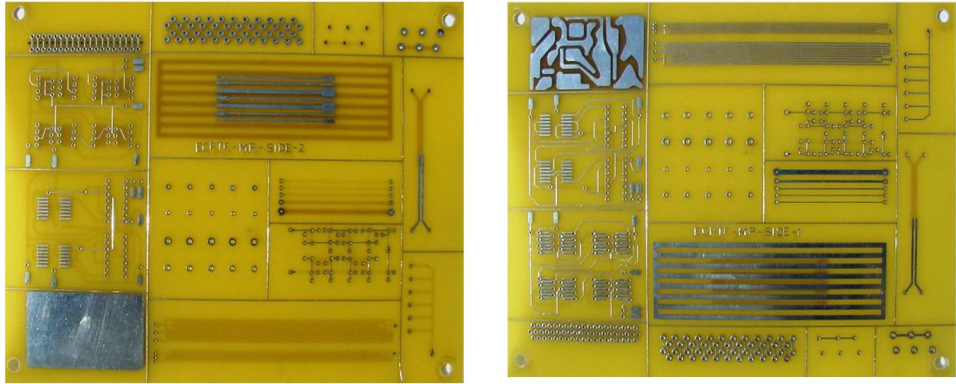
<b>Salient Features</b>	Drilling of 50 mil thick TMM10i laminate with ½ Oz basic Cu is being done on high speed CNC drilling machine followed by soft gold plating. After image transfer by using a negative photo film, gold and copper etching is carried out under the controlled condition which ensures minimum overhang and 100 micron lines and spacing. Routing process is being carried out for the required size on CNC drilling machine	
<b>Qualification test plan</b>	SAC/SRA/GEN/PQP/12.0/July 2013, Qualification Test plan for Gold plating / Solder Coating (using HAL) & pattern Generation Process of PCB fabrication with PTH on PTFE laminates. PID No.: SAC\ESSA\EFMG\PFD\PID\01\MARCH, 2014	
<b>Qualification Specifications</b>	<b>Description</b>	<b>Requirements</b>
	Laminate Type	RT5880
	Laminate Thickness	0.8mm
	Basic Copper thickness	½ oz (17 µm)
	Type of Finish	Gold finish
	Track width / Spacing (min)	0.250 mm / 0.250 mm
	Gold plating Thickness (min)	2 µm ( 2 to 8 µm)
	Hole Size (min)	0.3mm / 0.8mm
<b>Photograph</b>		

**50. DSB PTH and HAL finished PCB on Glass Epoxy FR5 grade (Tg 150 ° C) having laminate thickness 1.6mm & 1 Oz basic Copper**

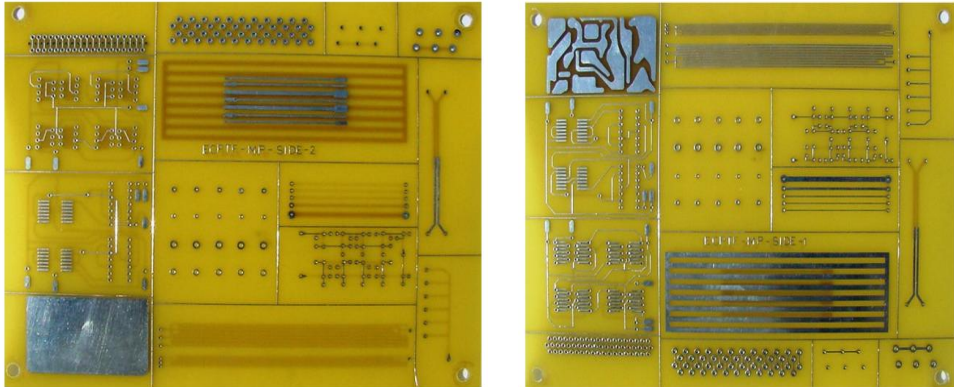
<b>Salient Features</b>	Process is being carried out by electro less copper plating for PTH with pattern up plating process on 1oz thick copper cladded 1.6 mm thick FR5 laminate. Tin plating is used as a etch resist during chemical etching process. Finally hot air leveling process is being done as final board finish. PTH and NPTH hole drilling and routing process are carried out on high speed CNC drilling machine.	
<b>Qualification test plan</b>	ISRO-PAX-302, Issue-1, "Test specification for printed circuit boards". PID No.: SAC\ESSA\EFMG\PFD\PID PFD/PID\04 REV 0\2013 APRIL 2013	
<b>Qualification Specifications</b>	<b>Description</b>	<b>Requirements</b>
	Laminate Type	FR5 (Poly-functional grade) , 1 oz each side, as per IPC-4101/23
	Laminate Thickness	1.6mm
	Basic Copper thickness	1oz (35 µm)
	Type of Finish	HAL Solder finish ( 4 to 30 µm)
	Track width / Spacing (min)	0.250 mm
	Hole Size (min)	0.5mm
<b>Photograph</b>	 <p style="text-align: center;">Side -2</p> <p style="text-align: center;">Side -1</p>	



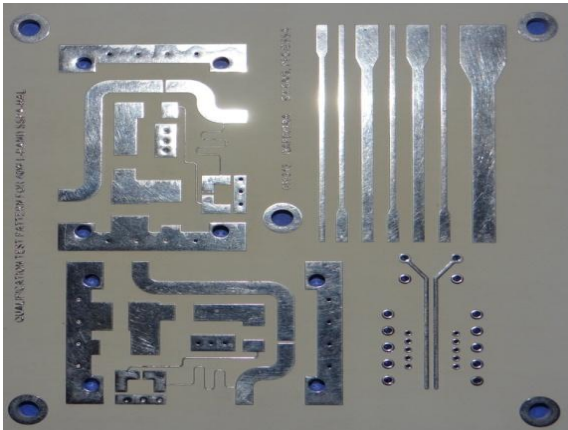
### 51. DSB PTH and HAL finished PCB on High Tg (175°C) Multifunctional Laminates having laminate thickness 0.8mm & 1 Oz basic Copper

<b>Salient Features</b>	Process is being carried out by electro less copper plating for PTH with pattern up plating process on 1oz thick copper clad High Tg (175°C) Multifunctional Laminates. To make the hole wall receptive to PTH process, desmaring process is being done. The Tin plating is used as a etch resist during chemical etching process. Hot air solder leveling process is being done to provide solderable finish. Drilling and routing is carried out on high speed CNC drilling machine.	
<b>Qualification test plan</b>	ISRO-PAX-302, Issue-1, "Test specification for printed circuit boards". PID No.: SAC\ESSA\EFMG\PFD\PID\05\ REV 0 \ 2013 MAY 2013	
<b>Qualification Specifications</b>	<b>Description</b>	<b>Requirements</b>
	Laminate Type	Glass epoxy laminate, 1 oz each side, as per IPC-4101, Nelco N4000-6 laminate
	Laminate Thickness	0.8mm
	Basic Copper thickness	1oz (35 µm)
	Type of Finish	HAL Solder finish ( 4 to 30 µm)
	Track width / Spacing (min)	0.250 mm
	Hole Size (min)	0.5 mm
<b>Photograph</b>	 <div style="display: flex; justify-content: space-around; margin-top: 5px;"> <span>Side - 2</span> <span>Side - 1</span> </div>	


## 52. DSB PTH and HAL finished PCB on High Tg (175°C) Multifunctional Laminates having laminate thickness 2.4mm & 2 Oz basic Copper

<b>Salient Features</b>	Process is being carried out by electro less copper plating for PTH with pattern up plating process on 2 oz thick copper clad High Tg (175°C) Multifunctional Laminates. To make the hole wall receptive to PTH process, desmaring process is being done. The Tin/Solder plating is used as a etch resist during chemical etching process. Hot air solder leveling process is being done to provide solderable finish. Drilling and routing is carried out on high speed CNC drilling machine.	
<b>Qualification test plan</b>	ISRO-PAX-302, Issue-1 "Test specification for printed circuit boards". PID No.: SAC\ESSA\EFMG\PFD\PID\05\ REV 0 \ 2013 MAY 2013	
<b>Qualification Specifications</b>	<b>Description</b>	<b>Requirements</b>
	Laminate Type	Glass epoxy laminate, 1 oz each side, as per IPC-4101, Nelco N4000-6 laminate
	Laminate Thickness	2.4 mm
	Basic Copper thickness	2oz (70 µm)
	Type of Finish	HAL Solder finish ( 4 to 30 µm)
	Track width / Spacing (min)	0.250 mm
	Hole Size (min)	0.5mm
<b>Photograph</b>	 <div style="display: flex; justify-content: space-around; margin-top: 5px;"> <span>Side - 2</span> <span>Side - 1</span> </div>	

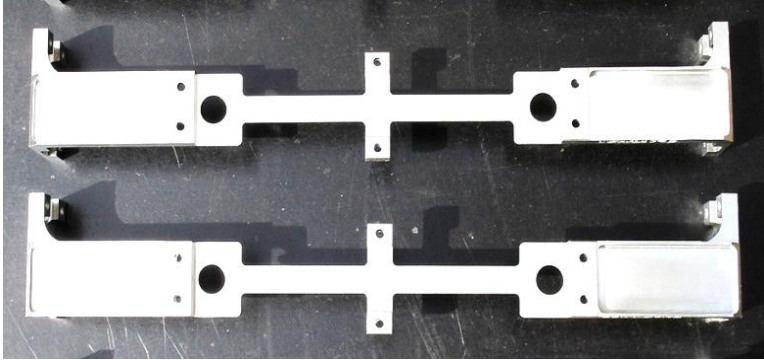
### 53. DSB PTH and HAL finished PCB on TMM10i having laminate thickness 100mil & 2 Oz basic Copper

<b>Salient Features</b>	Process is being carried out by electro less copper plating for PTH with pattern up plating process on 2 oz thick copper clad TMM10i. The Tin/Solder plating is used as a etch resist during chemical etching process. Hot air solder leveling process is being done to provide solderable finish. Drilling and routing is carried out on high speed CNC drilling machine.	
<b>Qualification test plan</b>	SAC/SRA/GEN/PQP/12.0/July 2013, Qualification Test plan for Gold plating / Solder Coating (using HAL) & pattern Generation Process of PCB fabrication with PTH on PTFE laminates. PID No.: PCB/PFD/ 01/ DEC.- 2010	
<b>Qualification Specifications</b>	<b>Description</b>	<b>Requirements</b>
	Laminate Type	TMM10i
	Laminate Thickness	100 mil
	Basic Copper thickness	2 oz (70 $\mu$ m)
	Type of Finish	HAL solder leveling finish
	Track width / Spacing (min)	0.100 mm
	HAL solder leveling thickness (min)	4 to 30 $\mu$ m
	Hole Size (min)	0.5 mm
<b>Photograph</b>		

**54. Electroless Nickel Immersion Gold on Semi-Rigid Cables for Space Use**



<b>Salient Features</b>	Electro-less Nickel Immersion Gold plating is being done on the semi - rigid cable to protect copper from environment and to provide the good solderable, less susceptible to whisker coating than conventional tin plating.	
<b>Qualification test plan</b>	PID: PCB -2 REV 1/PFD/APRIL 2012	
<b>Qualification Specifications</b>	<b>Description</b>	<b>Requirements</b>
	Semirigid Cable	Bare copper finish semi-rigid cable.
	Semirigid Cable Size	0.085" and 0.141" dia cable
	Type of Finish	ENIG gold finish
	Nickel plating Thickness	8-12 $\mu$
	Immersion gold plating Thickness	<0.1 $\mu$
<b>Photograph</b>		

**55. Tin plating on Copper Braid assembly**

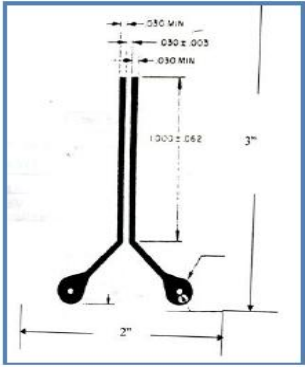
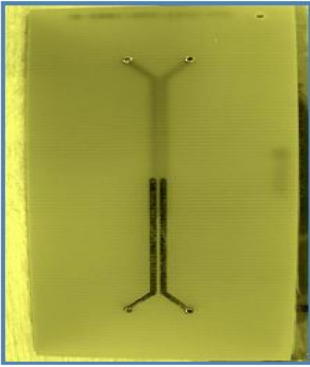

<b>Salient Features</b>	Cold fingers and copper braid assembly made from copper are required for better thermal conductivity for the IRS, CARTOSAT and RESOURCESAT series satellites. These copper components require tin plating mainly for solderability and corrosion resistance point view.	
<b>Qualification test plan</b>	PID: PCB / ECPTF / AUGUST 09	
<b>Qualification Specifications</b>	<b>Description</b>	<b>Requirements</b>
	Copper braid	Bare copper finish
	Type of Finish	Tin finish on braid assembly
	Tin plating	>12 microns
<b>Photograph</b>		



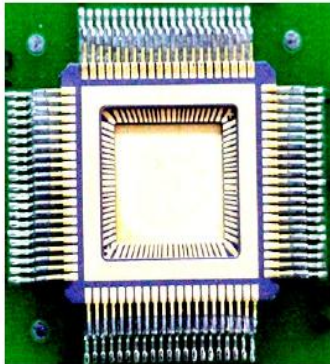
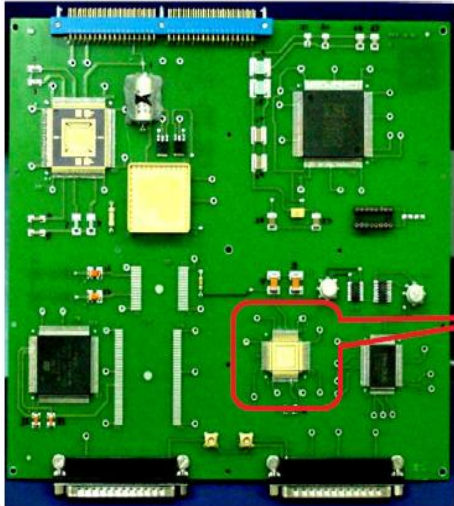
**56. Helical antenna strip making from 2mil thick Kapton material with 10z Cu**

<b>Salient Features</b>	Helical antenna strip having length 1200 mm and width 4 mm are generated on high speed CNC drilling machine from thin copper clad Kapton Flexible laminate. Pattern geometry shall be maintained constant throughout the length of strip and edges shall be free from burr.	
<b>Qualification test plan</b>	-	
<b>Qualification Specifications</b>	<b>Description</b>	<b>Requirements</b>
	Laminate Type	2 mil thick Kapton laminate
	Laminate length & width	1200 mm (typ.) 4 mm (typ.)
	Basic Copper thickness	35 micron
	Type of Finish	Bare copper, no additional finish
<b>Photograph</b>	 	

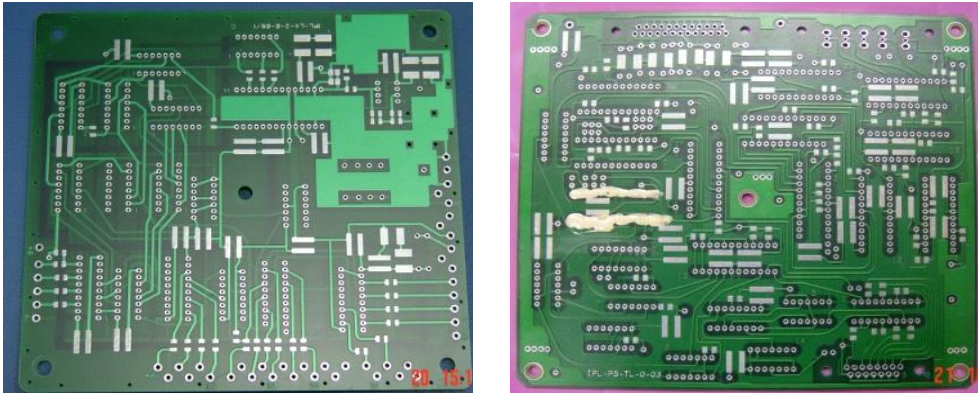
### 57. Vacuum deposition of Paraxylene (Parylene Conformal Coating Process) for Spaceborne PCB assemblies

<b>Salient Features</b>	The coating deposition process involves vaporisation, pyrolysis & sublimation of Parylene-C dimer from granules to uniform non conductive protective coating of 12-20 micron on wired PCB assemblies. It meets the requirements of MIL-I-46058 and has very low out-gassing properties. This process protects the wired PCBs from humidity, salts related effects which might stress the wired components/PCB during storage, transit.	
	<b>Parameter</b>	<b>Specification</b>
	Deposition Rate	5 Micron/Hr (Parylene C) 1 Micron/Hr (Parylene N)
	Max PCB Size	200x 175mm
	Card Batch	5 PCBs of Maximum Size
<b>Qualification test plan</b>	PID: SAC/ESSG/PFF -01-04	
<b>Major Specifications of Qualified Process</b>	<b>Parameter</b>	<b>Specification</b>
	Coating Material	Parylene C , Parylene N in Powder form
	Coating Thickness	15-25 Micron
	Insulation Resistance( $\Omega$ )	1.5 Terra Ohm min.
	Dielectric Withstand Voltage (DWV)	1500 V- 1min
<b>Photograph</b>	  	

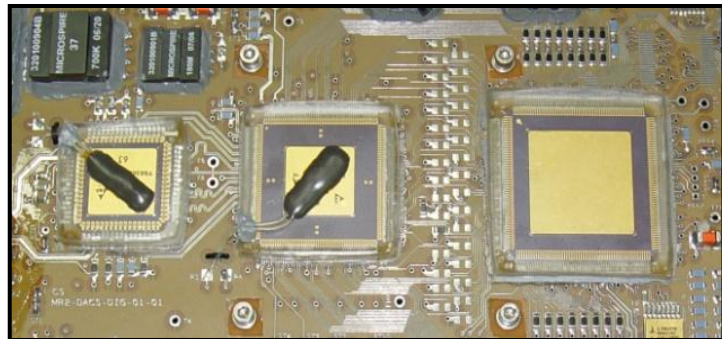

## 58. PCB Assemblies Comprising Of Through Hole & Fine Pitch Surface Mount Devices

Salient Features	Manual Soldering assembly of Mixed technology components described as below:		
	Parameter	Specification	
	Component Type	Leaded & SMD	
	Component Style	Resistor, Capacitor, DIP, Flat Pack, CQFP, D Sub/SMA Connectors	
	Pitch	Up to 16 Mil	
	Lead thickness	0.12 mm for CQFP & 0.3 mm Lead dia for PTH components	
	Maximum lead count	352 for fine pitch	
Qualification test plan	SAC\SRG\QPS-QAED\TR\23\2006 PID: SAC/ESSG/PFF/SMT/12/2005, Rev01		
Major Specifications of Qualified Process	Parameter	Specification	Achieved
	Pull Strength -CQFP	0.5 kgf	0.75-1.2 kgf
	Shear strength SMD	2.5 kgf	4 to 17.5 kgf
	Pull Strength	5 kgf	6-8 kgf
Photograph	<div></div>		

**59. Parylene Conformal Coating on SMOBC PCB**

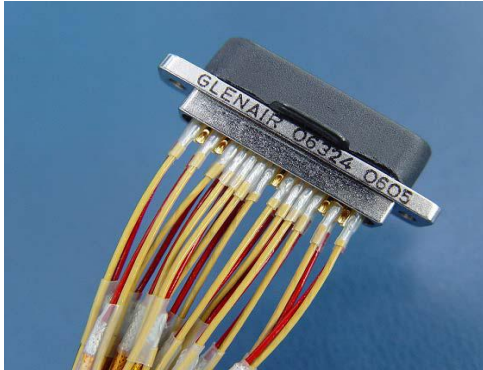
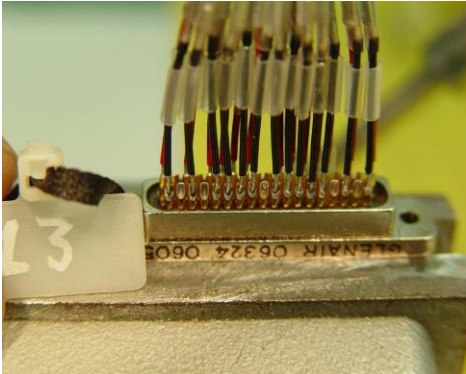
<b>Salient Features</b>	The coating deposition process involves vaporisation, pyrolysis & sublimation of Parylene-C dimer from granules to uniform non conductive protective coating of 12-20 micron on wired PCB assemblies. It meets the requirements of MIL-I-46058 and has very low out-gassing properties. This process protects the wired PCBs from humidity, salts, and ESD related effects which might stress the wired components/PCB during storage, transit.	
	<b>Parameter</b>	<b>Specification</b>
	Deposition Rate	5 Micron/Hr (Parylene C) 1 Micron/Hr (Parylene N)
	PCB Masking	Solder Mask over bare copper
<b>Qualification test plan</b>	SAC/QAED-SRG/QPS/TR/01/2006 PID: SAC/ESSG/PFF -01-04	
<b>Major Specifications of Qualified Process</b>	<b>Parameter</b>	<b>Specification</b>
	Coating Material	Parylene C , Parylene N in Powder form
	Coating Thickness	15-25 Micron
	Insulation Resistance( $\Omega$ )	1.5 Terra Ohm min.
	Dielectric Withstand Voltage (DWV)	1500 V- 1min
	PCB Size	300x300 mm
<b>Photograph</b>		

**60. Lead Forming, Mounting/Manual Soldering & Dam Formation (Device Encapsulation) using RTV DC 93-500 For CQFP / Flat Pack**

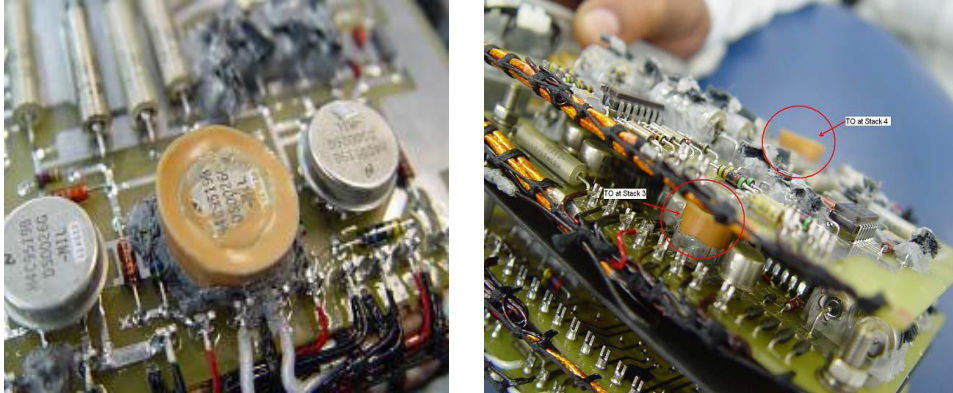
Salient Features	Process	Device Type	Lead thickness	Lead Count	Pitch
	Lead Forming, Mounting / Manual Soldering	CQFP, FP	0.12-0.25 mm	8-352	Up to 16 Mil
	Dam Formation (Device Encapsulation)	CQFP	0.12 mm	100 or more	20 Mil or less
Qualification test plan	PID: SAC/ESSG/PFF/01/05				
Major Specifications of Qualified Process	Test		Specification	Achieved Results	
	Pull Test-Fine Pitch CQFP/FPs		0.5 Kgf	0.75-1.2 Kgf	
Photograph					
					



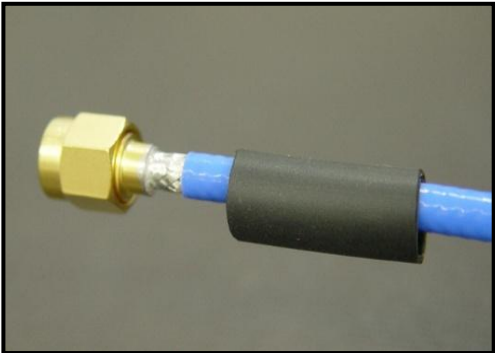
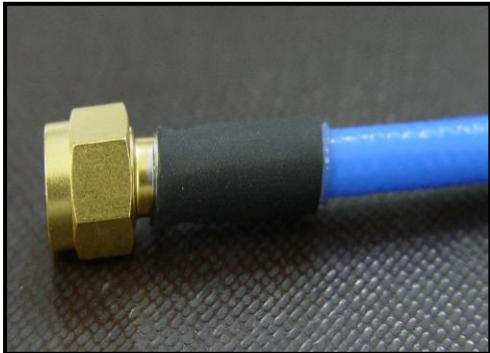
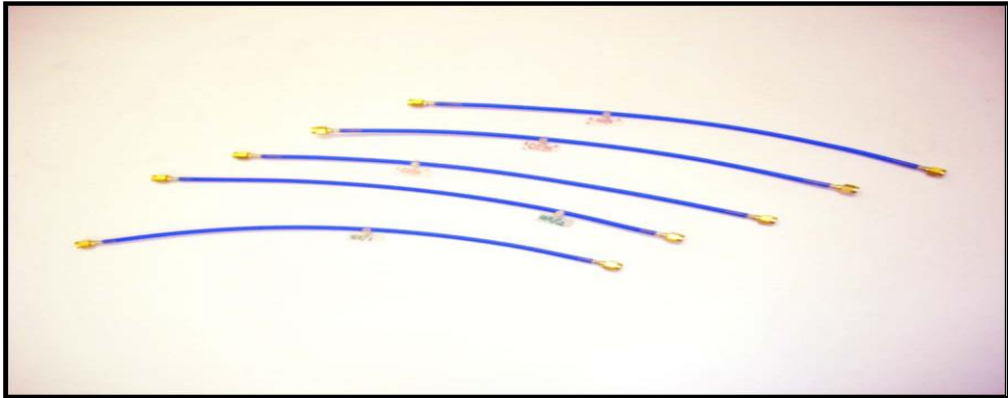
### 61. Micro D Connector (Solderable) Assembly with Polyamide Shielded Cables for TWSAT

Salient Features	Micro-D sub-miniature connectors offer significant reduction in size & weight, with excellent reliability. Available Pre-fabricated harness assemblies use wires crimped to the contacts which are permanently fixed in the shell with epoxy. However, with pre-crimped harness assemblies, flexibility for modifications in harness routing, changes in configuration and repair are severely restricted. The indigenous process development & qualification enables the effective utilisation of solderable cup micro d connector with desired configuration with a facility of modification at any stage. Micro Ds are comparatively lesser in weight (60%) & volume (40%) with respect to Normal D Sub for same pin count.			
	Connector	Pin/Plug Pitch	Wire gauge	Maximum Pin/Plug Count
	Micro D	1.27 mm	26 & 28 AWG	37
Qualification test plan	QPS-QAED/2007/45 PID: SAC/ESSG/EFTF/PFF -01 MAY- 2007			
Major Specifications of Qualified Process	Specification	Requirement (Mil-DTL-83513)		Achieved
	Contact Resistance	32 mΩ Max		5.7- 6.8 mΩ
	Wire Pull Strength	2.2 Kg		2.7-7 Kg
Photograph	<div></div> <div></div>			

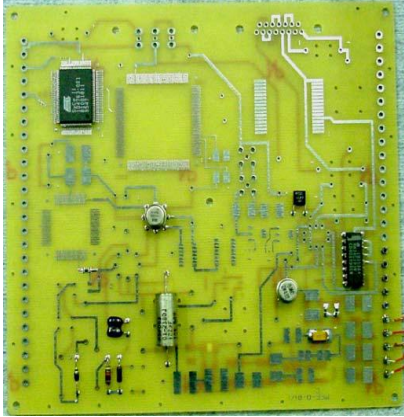

**62. Thermally Conductive H-74 Epoxy Application on TO Can IC's in OCM payloads of OS-II**

<b>Salient Features</b>	Global Area Coverage (GAC) by OCM-II P/L to meet the demand from the users across the globe has necessitated increasing payload 'ON' period (from 12 to 40 minutes) for several consecutive orbits thus reducing the 'Cool Off' period to 60 minutes before scanning the next orbit. Under Such conditions thermal team has estimated the ambient temperature of payload to rise to 42°C, which poses the risk of certain TO can devices to reach at the junction temperature. For adequate heat dissipation, the process is developed, qualified & successfully utilised in OCM-II payload.
<b>Qualification test plan</b>	Eval. Report -29/10/2007 Annex-B PID: SACESSGEFTFPFF -01-Nov- 2007
<b>Major Specifications of Qualified Process</b>	Process is adequate in thermal dissipation in active devices by 20-30 deg C depending upon the configuration.
<b>Photograph</b>	


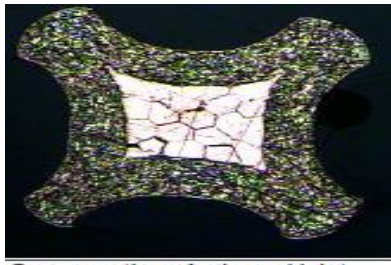

### 63. Assembly Of “Huber Suhner” SMA Solderable Connectors (11 SMA 50-3-15) On MF-141 Coaxial Cable

Salient Features	Huber Suhner make MULTIFLEX microwave cables are the flexible alternative to SEMI RIGID cables. They are used in commercial and military RF and microwave airborne systems, communications systems, satellite ground stations.		
	Cable Type	Cable Diameter	Frequency of Operation
	Multi Flex-141	0.141 Inch	Up to 18 Ghz
Qualification test plan	PID: SAC/ESSG/EFTF/EFF/PID/O1		
Major Specifications of Qualified Process	Connector Type	Interconnection Process	
	SMA Solderable Connectors ( 11 SMA 50-3-15)	Soldering	
Photograph			
	 		

#### 64. Vapour Phase Parylene Conformal Coating of PCB Assemblies utilising PDS 2060 PC System

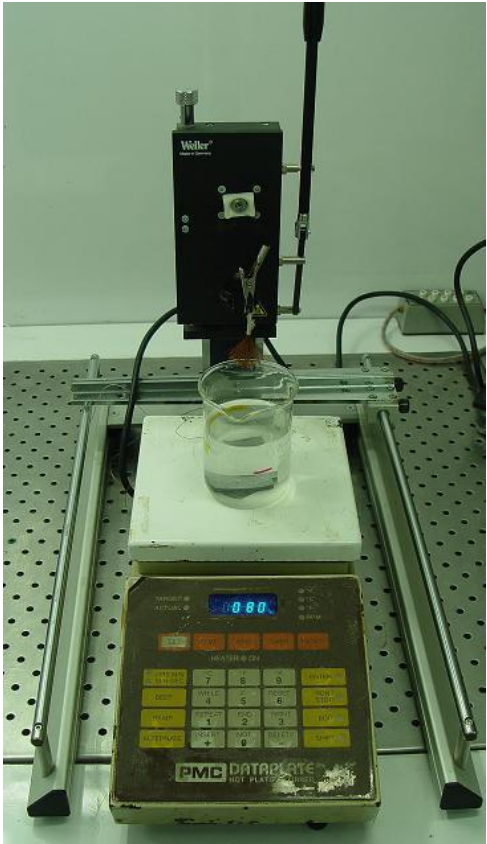


Salient Features	Parameter		Specification
	Coating Material		Parylene C, Parylene N in Powder form
	Coating Thickness		15-25 Micron
	Deposition Rate		5 Micron/Hr (Parylene C) 1 Micron/Hr (Parylene N)
	PCB Size		300x300 mm
	Card Batch		10 PCBs of Maximum Size
Qualification test plan	SAC/SRG/QPS-QAED/TR/17/2009 PID: SACESSGEFTFPFF -20-June-2009		
Major Specifications of Qualified Process	Parameter	Specification	Achieved
	Insulation Resistance( $\Omega$ )	1.5 Terra Ohm min.	1.7-6 Terra Ohm
	Dielectric Withstand Voltage (DWV)	1500 V- 1min	1500 V- 1min No evidence of flashover, arching or de-lamination was found during the test. All the test samples meet the requirements
Photograph	 		

**65. Crimpable Micro D Connector Harness Assembly process**



Salient Features	In new package design of advance projects, use of Micro D connectors are essential as a step towards miniaturizations & weight saving. Crimpable Micro-D Connectors are having inherited advantage of small foot print due to its miniature size and les weight as compared to Normal D sub Connectors. In TWSAT, Solderable Cup Micro d Connectors was qualified and implemented and as an upgradatation, crimp version of Micro-D Connectors have also successfully taken up for harness & assembly qualification.				
	Connector	Pin/ Plug Pitch	Wire gauge	Wire Type	Maximum Pin/Plug Count
	Micro D	1.27 mm	26/28 AWG	Polyamide, Spec-55, LVDS, Polyamide Shielded cables, RG-316, TP	37
Qualification test plan	QPS-QAED/2010/79 PID: SACESSAEFTFPFF H Crimp -10-01				
Major Specifications of Qualified Process	Specification	Requirement (Mil-DTL-83513)		Achieved	
	Contact Resistance	32 mΩ Max		8 mΩ	
	Wire Pull Strength	30N (28AWG wire) 45N (26AWG wire)		35-40 N(28AWG wire) 55-70 N(26AWG wire)	
Photograph	<div><div></div><div><p>Cross section of crimped joint</p></div></div>				
					



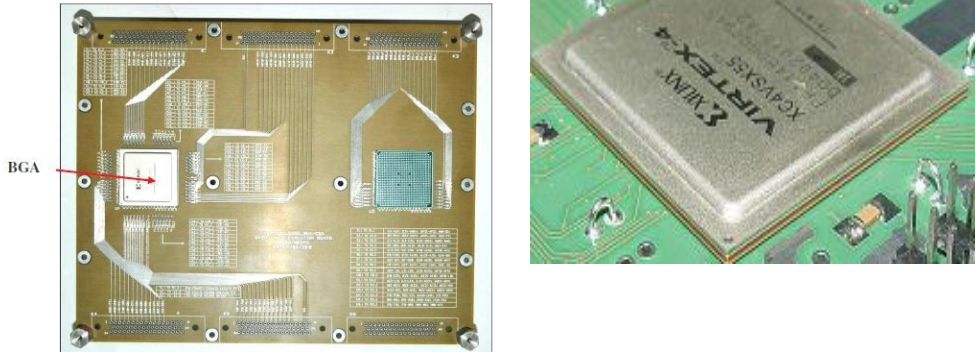
**66. Multistrand Enamelled Copper wire (Litz) Insulation removal & Tinning**

<b>Salient Features</b>	In new package design of High power electronic power conditioner for 100 W solid state power amplifiers (GSAT-7), coils made of Multistrand enamelled copper wires is to utilized due to their high current carrying capacity. Enamel removal of these coils requires specialized procedure which ensures the full insulation removal from each individual wire thread which is very essential for optimum performance of the coil	
<b>Qualification test plan</b>	Eval Report-06/02/08 PID: SACESSAEFTFPFF S TINNING -11-01	
<b>Major Specifications of Qualified Process</b>	<b>Process</b>	<b>Method</b>
	Insulation Removal	Chemical Insulation removal ( 40% W/V NaOH Solution )
	Tinning	Solder dip(Sn60/Pb40)
<b>Photograph</b>	  <p>Wire Bunch after insulation removal</p> 	

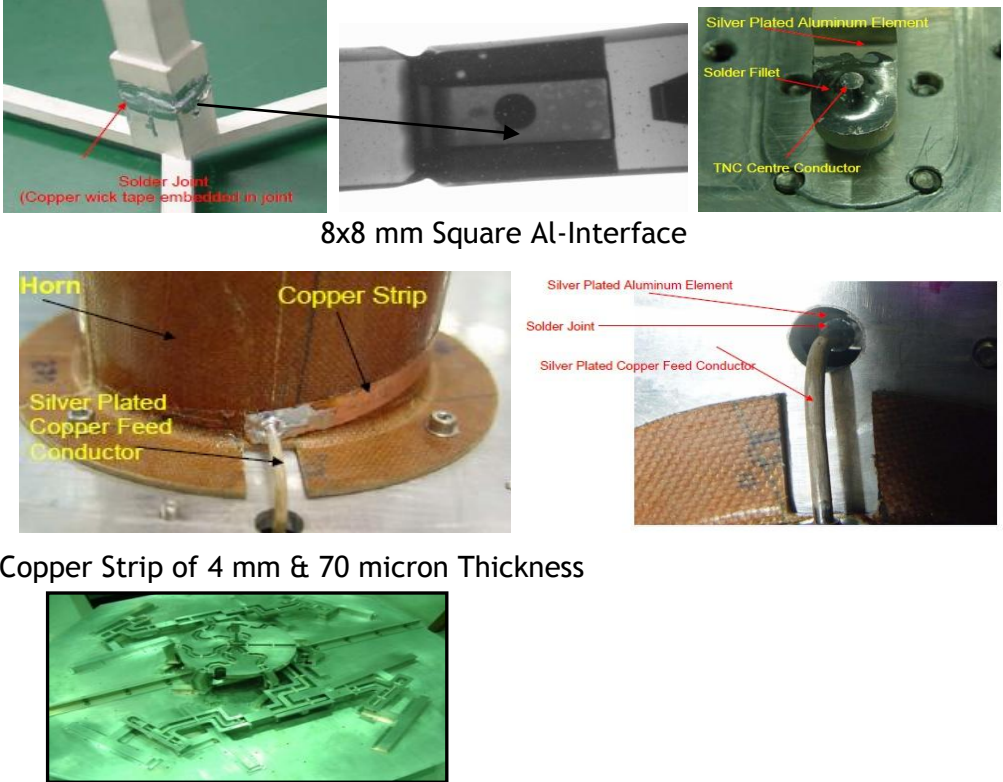
**67. Realisation of Ortho-Mode Transducer with solder as a Metal Joinery process for MM wave Sounder**

<b>Salient Features</b>	Soldering activities are considered to be the prime assembly mechanism for electronic components wiring on printed circuit boards. Use of Solder joint exclusively for mechanical, structural application is rare as mechanical structures are designed to endure greater magnitude of thermal and vibration loads compared to electronic packages. Soldering as a mechanical joining method was developed & qualified to realise the complex OMT feeds.	
<b>Qualification test plan</b>	PQ/SOLDERING/03 PID: SAC/SRA/QAMD/TR/00/APRIL-2011	
<b>Major Specifications of Qualified Process</b>	<b>Name of Test</b>	<b>Results</b>
	Tensile test	100 N/mm <sup>2</sup>
	Shear test	30 N/mm <sup>2</sup>
<b>Photograph</b>	 	

**68. Assembly of Ball Grid Array (BGA) on Space hardware with Hot Gas Reflow**

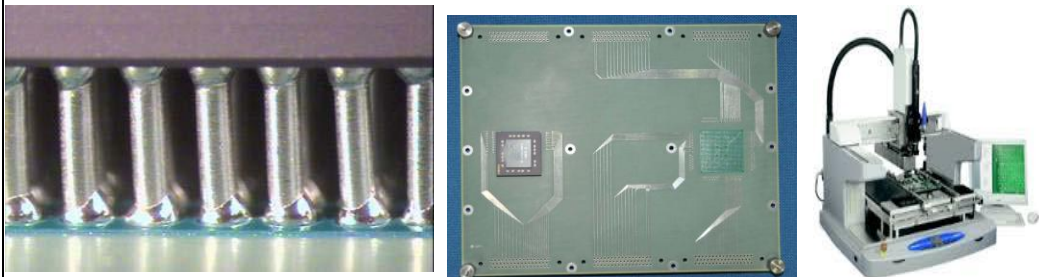
<b>Salient Features</b>	Advance electronic packages demand miniaturization of components with higher pin counts, & convergence of functionalities with robustness. In order to accommodate the increasing number of I/Os needed, the peripheral QFP technology is forced to an ever finer lead pitch with thinner and more fragile leads. The BGAs, taking advantage of the area under the package for the solder sphere interconnections, satisfies the more number of I/O demand using a far coarser pitch. BGAs offer approximately 50% increased silicon density and 60% effective size reduction as compared to QFP devices.			
	<b>Balls</b>	<b>Ball dia</b>	<b>Pitch</b>	<b>Solder Material</b>
	1148	0.65 mm	40 mil	Sn63Pb37
<b>Qualification test plan</b>	SRA/QAPD-QAEG/2011/80 PID: SACESSAEFMGPEFDSREFLOW-10-03			
<b>Major Specifications of Qualified Process</b>	The BGA soldering process using Hot Air Reflow System (ONYX-29) with following configuration can be declared as qualified for field life of 4.3 years in LEO orbit with field operation temperature 0°C to +40°C.			
<b>Photograph</b>				

### 69. Solder as a Metal Joinery process for S & L5 Band Helical Antenna feed soldering for IRNSS series

<b>Salient Features</b>	Process development includes soldering of mechanical antenna parts for flexibility and better return loss (-22db) performance. Elements are high thermal dissipative metal parts and process was developed to compensate the heat losses during soldering. Feed was also modified to self align itself prior to soldering.
<b>Qualification test plan</b>	SRA/QAPD-QAEG/2012/23 PID: SACESSAEFMGPEFD SOL-HELIX-12-04
<b>Major Specifications of Qualified Process</b>	<p>Solder as metal joinery media has been successfully utilized &amp; qualified for following four types of configuration:</p> <ul style="list-style-type: none"> <li>➤ Soldering of two Silver Plated Aluminum Elements</li> <li>➤ Soldering Activity of Silver plated aluminum element with silver plated copper feed wire</li> <li>➤ Soldering of gold plated TNC connector with silver plated aluminum element</li> <li>➤ Soldering of Silver plated copper feed wire with copper strip on horn</li> </ul>
<b>Photograph</b>	 <p>8x8 mm Square Al-Interface</p> <p>Copper Strip of 4 mm &amp; 70 micron Thickness</p>

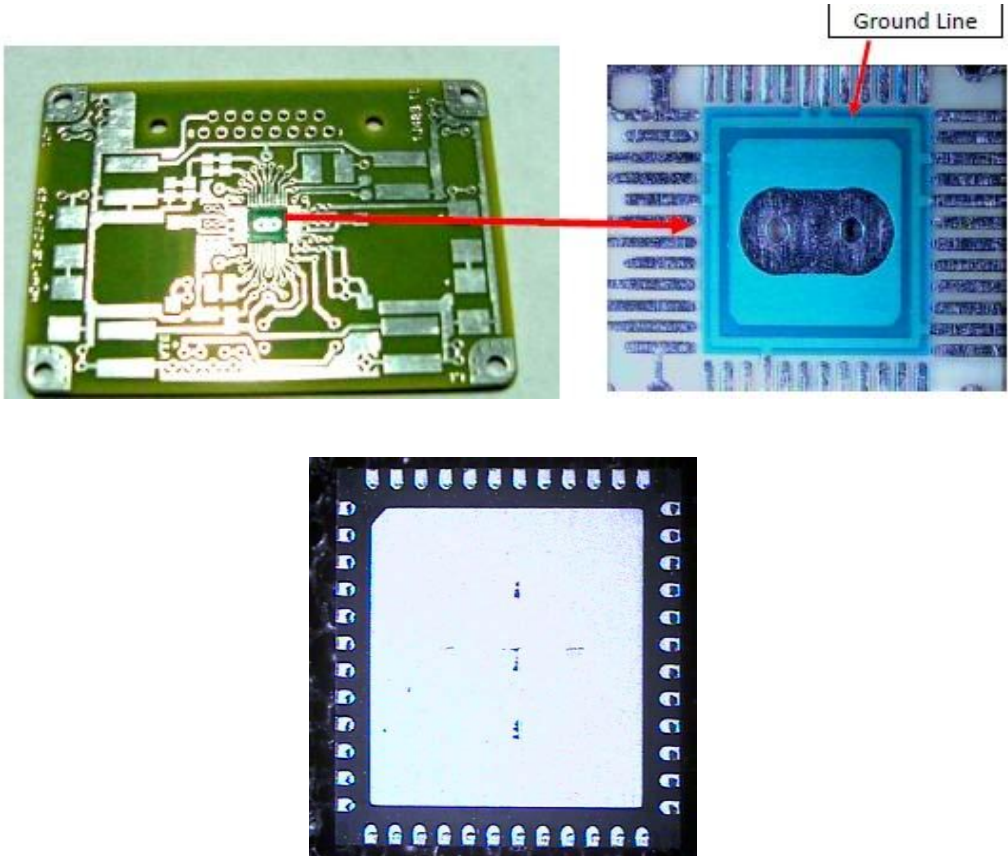


## 70. Ceramic Column Grid Array (CCGA) Assembly & Soldering process development with Hot Gas Reflow

Salient Features	CCGA components are latest packaging in the family of Area Array Devices & similar with BGA in terms of interconnection density & area, however differs in interconnection length & weight. As compared to BGAs, CCGAs are less susceptible to CTE mismatch related failures which is a prominent failure mode for BGAs, thus providing reliability by component design itself. CCGAs also offer ease of processing like cleaning/inspection of outer rows & few inner rows due to the increased gap between device body & PCB surface.		
	CCGA Device Characteristics		
	Device Size	35x35 mm	
	Device Material	Multilayer Ceramic(CTE~ 6-8 ppm/ ° c)	
	Substrate thickness	3 mm	
	Device Weight	~23 grams	
	Column Material	90Pb10Sn	
	Column attach	CLASP (Pd Doped Sn63/Pb37)	
	Column dia	~0.52mm	
	Column pitch	1mm	
	Column Height	2.21 mm	
Qualification test plan	SRA/QAPD-QAEG/2012/49 PID: SAC/ESSA/EFMG/PEFD/S/REFLOW-12-01		
Major Specifications of Qualified Process	The CCGA assemblies have successfully passed the accelerated thermal cycling test and no failure was observed even after 1200 cycles due to solder-joint. This is equivalent to		
	Test Condition	Field Environment	Estimated life
	-55°C to +105°C with ramp rate of 3°C/minute	LEO Orbit with 90 minutes cycle, Operating temp. 0°C to +40°C	7 Years
		GEO Orbit with 24 hrs cycle, Operating temp 0°C to +40°C	45 Years
Reliability figure for CCGA joint is calculated to be 0.99974237.			
Photograph			



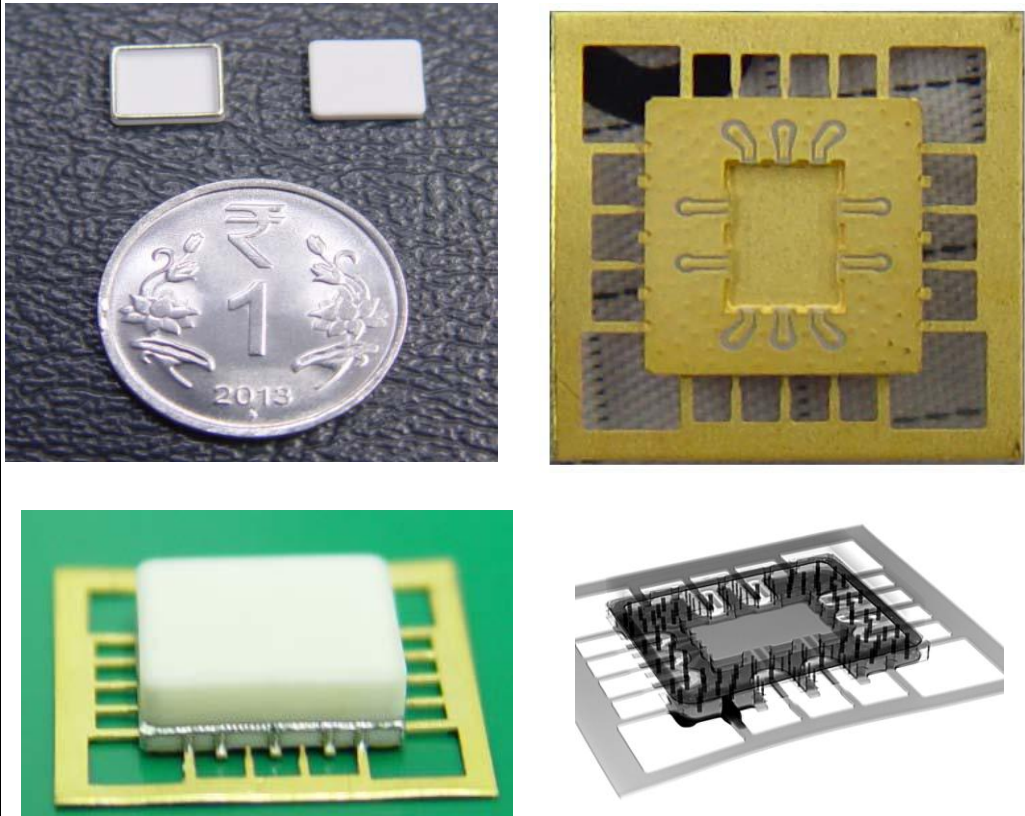
### 71. Quad Flat Pack No Lead (QFN) Assembly & Soldering by Hot Gas Reflow for Mars Orbiter Mission

<b>Salient Features</b>	<p>QFN (MAX1978/MAX1979) packages are planned to be used in temperature controller circuits in TIS payload for MARS mission. QFN (Quad Flat Pack with No Lead) packaging has no leads in sides and essentially has a large thermal pad (Ground Lug) in the centre. These are plastic packages with bottom termination and are being used for the first time in space payload. Soldering &amp; assembly process has been successfully developed &amp; qualified for Flight model subsystems.</p>	
<b>Qualification test plan</b>	<p>SRA/QAEG-QAPD/2013/17 PID: SACESSAEFMGPEFDSS201302</p>	
<b>Major Specifications of Qualified Process</b>	<b>Parameter</b>	<b>Specification</b>
	Pitch	20 Mil
	Pads	49
<b>Photograph</b>	 <p>The photograph section contains three images. The top-left image shows a green printed circuit board (PCB) with a Quad Flat Pack No Lead (QFN) package mounted on it. A red arrow points from the package to a magnified view on the top-right. This magnified view shows the package's central thermal pad and surrounding pads, with a label 'Ground Line' and a red arrow pointing to the central pad. The bottom image is a top-down view of the QFN package, showing its square shape and the central pad.</p>	

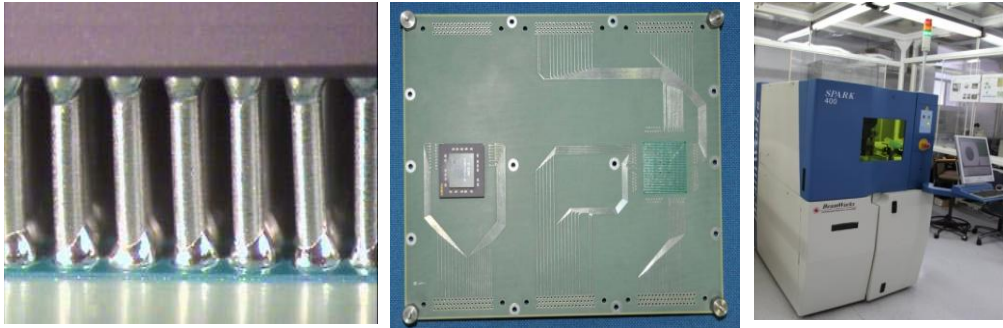
## 72. Micro Camera Assembly process for Chandrayaan-II Rover

<b>Salient Features</b>	<p>For Chandrayaan-II landing rover configuration requires miniature camera module for imaging purposes. The realization of the flight hardware requires assembly &amp; soldering of Plastic Body Camera Module on the Multi Layer PCB. As the camera body is made of the plastic material, and the lead pattern is of QFN types (without leads) conventional reflow option is not feasible considering degradation of the camera body itself. A novel method was developed which incorporates cutting a window (analogous in size with camera pad layout) on the PCB while making connection through the half open PTH barrels with the help of fine leads (CQFP leads)</p>
<b>Qualification test plan</b>	<p>SRA/QAEG-QAPD/2013/12 PID: SACESSAEFMGPEDS2013-1</p>
<b>Major Specifications of Qualified Process</b>	<p style="text-align: center;"><b>Camera Specifications</b></p> <p>Exposed Camera Pads (From Back): 0.6mm Cut-Out Size : 5.2 mm x 5.2 mm</p> <p>PCB (Bottom Layer)</p>
<b>Photograph</b>	

### 73. Lid-Sealing Process of Hermetic Package (GMR-A3253) for MMIC, using Hot Gas Reflow Soldering (ONYX 29)

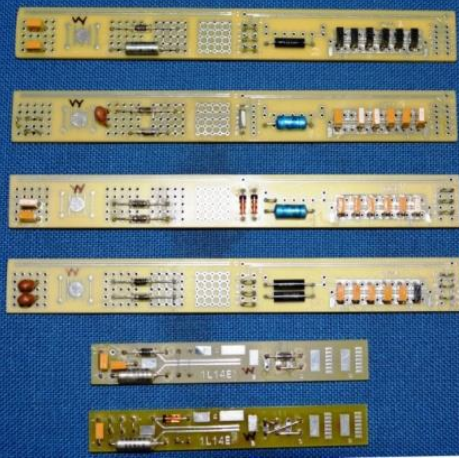

<b>Salient Features</b>	Packaging of bare MMIC die was required to be carried out for the on-going activity of GEOSAT Programme. The requirement generated due to delay in the delivery of FM packaged MMIC mixer devices from M/s OMMIC. It was decided to develop in-house lid-sealing process to realize packaged devices with available FM MMIC die by improvising the existing hot gas reflow soldering system.		
<b>Qualification test plan</b>	SAC/SRA/GEN/PQR/8.0/May,2015 PID: SAC/ESSA/EFMG/PEFD/S/2013/03		
<b>Major Specifications of Qualified Process</b>	<b>Parameter</b>	<b>Specification</b>	<b>Achieved</b>
	Fine Leak	$< 5 \times 10^{-8}$ atm. cc/sec He	$1.5 - 4 \times 10^{-8}$ atm. cc/sec He
	Gross leak	Nil leak	Nil leak
<b>Photograph</b>			

#### 74. Reflow Soldering of Ceramic Column Grid Array (CCGA) with LASER

<b>Salient Features</b>	CCGA components are latest packaging in the family of Area Array Devices & similar with BGA in terms of interconnection density & area, however differs in interconnection length & weight. As compared to BGAs, CCGAs are less susceptible to CTE mismatch related failures which is a prominent failure mode for BGAs, thus providing reliability by component design itself. CCGAs also offer ease of processing like cleaning/inspection of outer rows & few inner rows due to the increased gap between device body & PCB surface.	
	<b>CCGA Device Characteristics</b>	
	Device Size	35x35 mm
	Device Material	Multilayer Ceramic(CTE~ 6-8 ppm/ c)
	Substrate thickness	3 mm
	Device Weight	~23 grams
	Column Material	90Pb10Sn
	Column attach	CLASP (Pd Doped Sn63/Pb37)
	Column dia	~0.52mm
	Column pitch	1mm
	Column Height	2.21 mm
<b>Qualification test plan</b>	Eval. Report12/06/2015 PID: SAC/ESSA/EFMG/PEFD/LASER-S/06/2015	
<b>Major Specifications of Qualified Process</b>	The CCGA assemblies have successfully passed the accelerated thermal cycling test and no failure was observed even after 1200 cycles due to solder-joint. Qualification report is awaited.	
<b>Photograph</b>		




## 75. Conformal Coating Removal using Micro Blasting System

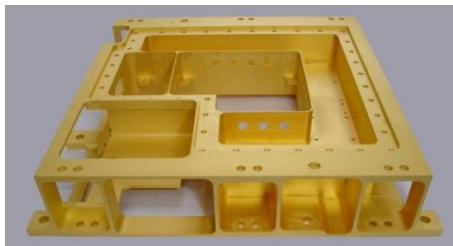
<b>Salient Features</b>	<p>Any rework or component replacement or incorporation of jumper wires, etc. is cumbersome on a conformably coated PCB, as this requires special skills and a controlled localized removal of the conformal coating (CC). However, even with utmost care, manual removal of CC may leave physical damage like scratches &amp; cuts on the PCB laminate /conductor. The non-contact CC removal process, using the “Swam-Blaster” system, helps prevent this damage and gives uniform removal as well. Swam-Blaster (Crystal Mark Inc. make) is a machine that provides controlled CC removal. The swam-blaster machine has two controls for quantity of powder and for air pressure, such that there desired combination of powder-quantity and air-pressure can be optimized. The powder is not soluble in IPA and cleaned away by this cleaning agent.</p>		
<b>Qualification test plan</b>	<p>SAC/SRA/PEFD/10/May,2015 PID: SAC/ESSA/EFMG/PEFD/LASER-S/04/2015</p>		
<b>Major Specifications of Qualified Process</b>	<b>Coating Type for removal</b>	<b>Thickness for removal</b>	
		<b>Requirement</b>	<b>Max Thickness which can be removed</b>
	Parylene C	25 Micron	Tested up to 150 microns
	Polyurathene	50 Microns	Tested up to 150 microns
<b>Photograph</b>			
			



**76. Gold Plating on Aluminum Alloy 6061**

Process UID No	STPD / ST - 01			
Brief Description	Developed and qualified the process of Gold Plating on Aluminum Alloy 6061T6 with Electroless nickel undercoat for attaining good EMI/EMC, Corrosion Protection & solderability for subsystem components of various satellites.			
Technical Specifications				
Thickness of Electroless Nickel undercoat	8 -10µm			
Thickness of Gold plating	1µm			

**77. Gold Plating on Aluminum 6061T6 Alloy**

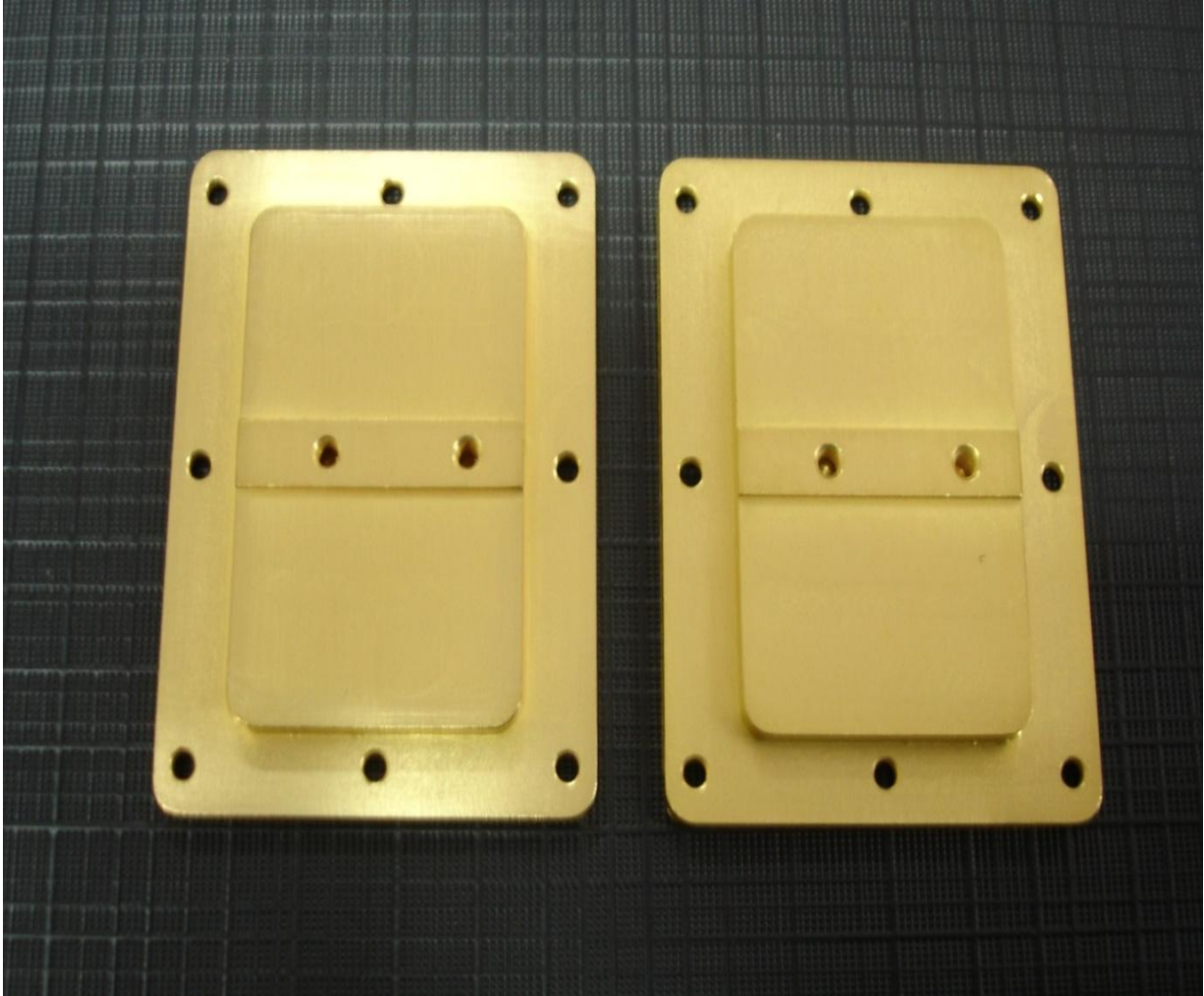
Process UID No	STPD / ST - 02		
Brief Description	Developed and qualified the process of Gold Plating on Aluminum Alloy 6061T6 with Electroless nickel undercoat for attaining good EMI/EMC, Corrosion Protection & solderability for subsystem components of various satellites.		
			
Technical Specifications			
Thickness of Electroless Nickel undercoat		8 -10µm	
Thickness of Gold plating		2µm	

**78. Gold Plating on Kovar with Nickel Undercoat****Process UID No**

STPD / ST - 03

**Brief Description**

Developed and qualified the process of Gold Plating on Kovar with Nickel undercoat for attachment of gold plated Alumina substrates to carrier plates.

**Technical Specifications**

Thickness of Nickel undercoat

3 - 4 $\mu$ m

Thickness of Gold plating

1.25 - 1.5 $\mu$ m

**79. Gold Plating on Invar****Process UID No**

STPD / ST - 04

**Brief Description**

Developed and qualified the process of Gold Plating on Invar for solderability and corrosion protection for Induction posts.

**Technical Specifications**

Thickness of Gold plating: 6µm

**80. Gold Plating on SS-304****Process UID No**

STPD / ST - 05

**Brief Description**

Developed and qualified the process of Gold Plating on SS-304 for attaining good Electrical conductivity and good corrosion protection for SS-304 screws used in satellites.

**Technical Specifications**

Thickness of Gold plating

6 $\mu$ m

**81. Gold Plating on Magnesium AZ31B Alloy**


Process UID No	STPD / ST - 06
Brief Description	Developed and qualified the process of Gold Plating on Magnesium AZ31B alloy on PCPU boxes for attaining Corrosion Protection, good EMI/EMC & solderability.
	
<b>Technical Specifications</b>	
Thickness of Gold plating	6µm

**82. Gold Plating on Silvar**


Process UID No	STPD / ST - 07
Brief Description	Developed and qualified the process of Gold Plating on Silvar (which provides an improved thermal conductivity along with a CTE that matches that of alumina substrate).
	
<b>Technical Specifications</b>	
Thickness of Nickel undercoat	3 - 4 µm
Thickness of Gold plating	1.5 - 2.5 µm



**83. Gold Plating on CE-7**

Process UID No	STPD / ST - 08	
Brief Description	Developed and qualified the process of Gold Plating on CE-7, which has low CTE.	
		
Technical Specifications		
Thickness of Electroless Nickel	11-12 $\mu\text{m}$	
Thickness of Gold plating	2 - 3 $\mu\text{m}$	

**84. Silver Plating on Aluminum 6061-T6 Alloy**

Process UID No	STPD / ST - 09	
Brief Description	Developed and qualified the process of Silver Plating on Aluminum 6061-T6 Alloy on various components (Ku and Ka band) like waveguides, adaptors, HRFs, Filters for electrical conductivity & solderability, corrosion protection and good base for thermal control coatings.	
		
Technical Specifications		
Thickness of Silver	5 - 8μm	

**85. 25-30  $\mu$ m Silver Plating on Aluminum 6061-T6 Alloy**

Process UID No	STPD / ST - 10
Brief Description	Developed and qualified the process of Silver Plating on Aluminum 6061-T6 Alloy on various components like UHF, Filters for electrical conductivity & solderability, corrosion protection and good base for thermal control coatings.

**Technical Specifications**

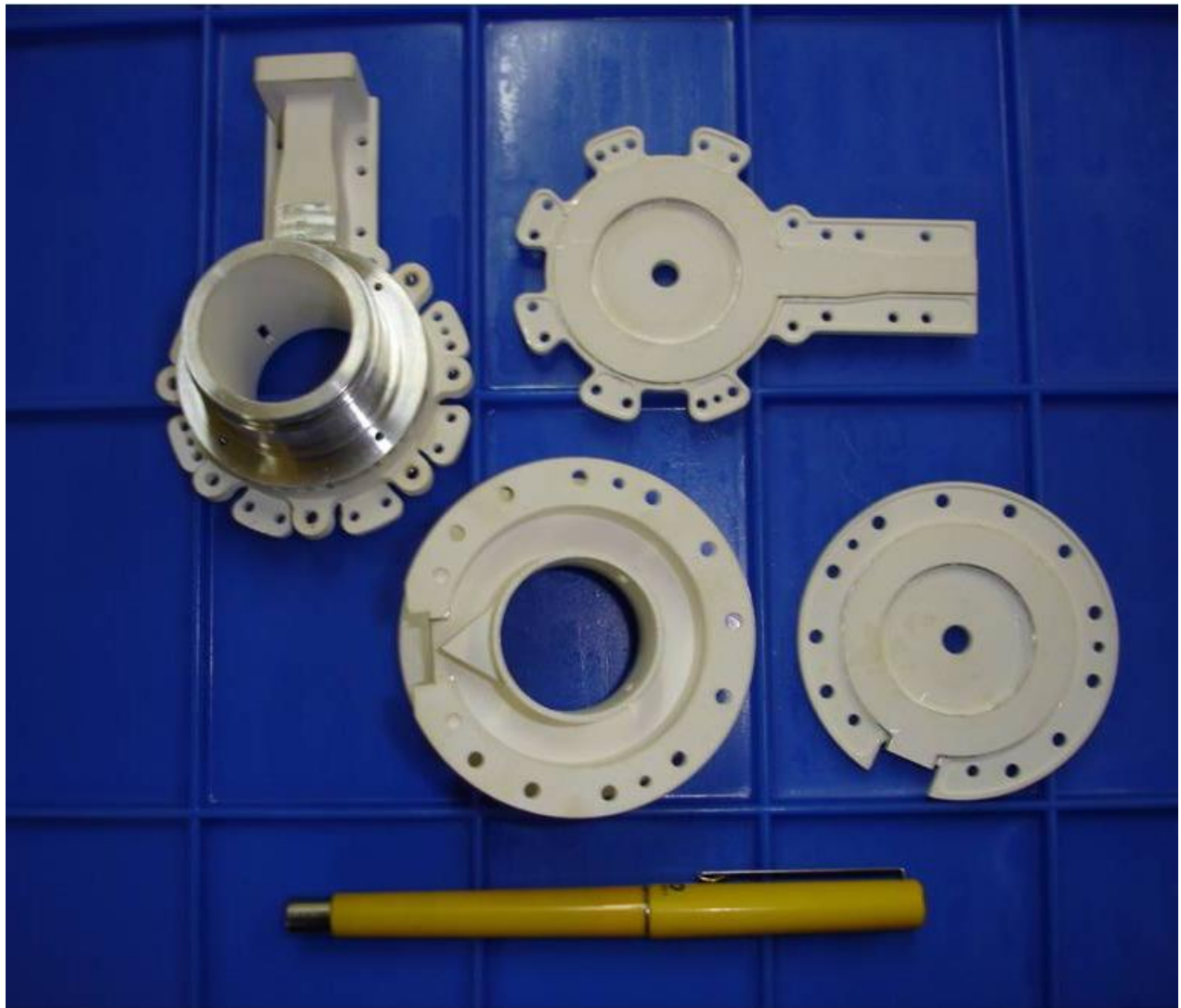
Thickness of Silver	25 - 30 $\mu$ m
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**86. Silver Plating on Aluminum 2024 Alloy****Process UID No**

STPD / ST - 11

**Brief Description**

Developed and qualified the process of Silver Plating on Aluminum 2024 Alloy on various components like rotary joints for good electrical conductivity & solderability, corrosion protection and good base for thermal control coatings.

**Technical Specifications****Thickness of Silver**5 - 8 $\mu$ m

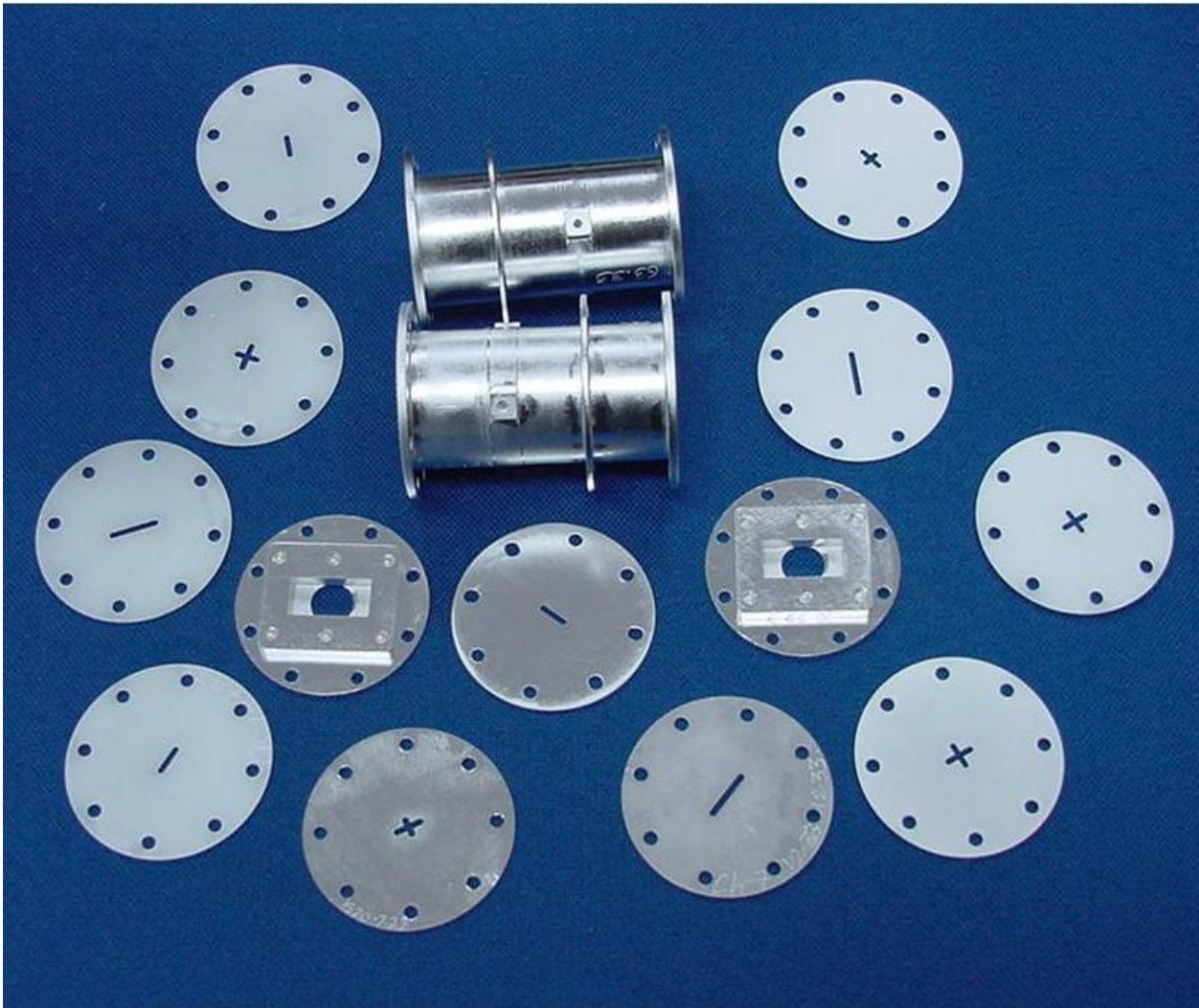


**87. Silver Plating on Invar****Process UID No**

STPD / ST - 12

**Brief Description**

Developed and qualified the process of Silver Plating on Invar manifolds, cavities, iris, adaptors for good electrical conductivity & solderability and good base for thermal control coatings.

**Technical Specifications****Thickness of Silver**5 - 8 $\mu$ m

**88. Silver Plating on Copper Helix****Process UID No**

STPD / ST - 13

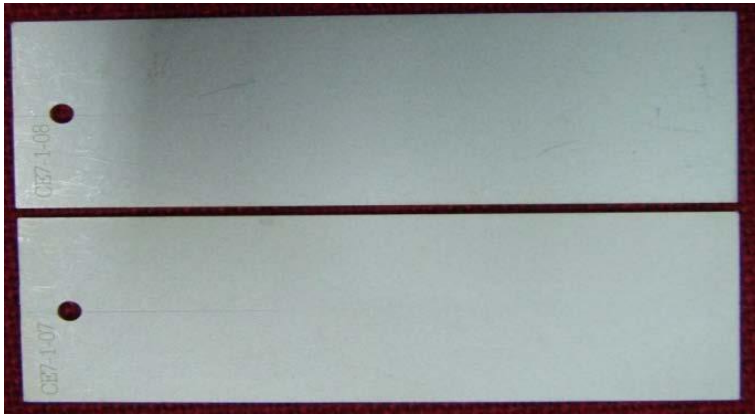
**Brief Description**

Developed and qualified the process of Silver Plating on copper helix conductors for solderability to helix and feed network.


**Technical Specifications****Thickness of Silver**5 - 8 $\mu$ m



**89. Silver Plating on CE-7**

Process UID No	STPD / ST - 14
Brief Description	Developed and qualified the process of Silver Plating on CE-7, which has low CTE.
	
<b>Technical Specifications</b>	
Thickness of Electroless Nickel	10-12µm
Thickness of Silver	8-9µm

**90. Silver Plating on Copper-Beryllium**

Process UID No	STPD / ST - 15
Brief Description	Developed and qualified the process of Silver Plating on Copper-Beryllium alloy with nickel undercoat for use as shims between waveguides.
	
<b>Technical Specifications</b>	
Thickness of Silver	4-7µm

**91. Electroless Silver Plating on Aluminum 6061T6**

Process UID No	STPD / ST - 16
Brief Description	Developed and qualified Electroless silver plating on Aluminum without passing electrolytic current between anode and cathode. This solves the problem of plating silver inside difficult to approach cavities like small cross sectional waveguides and similar components.
	
<b>Technical Specifications</b>	
Thickness of Electroless Nickel	8 - 12 $\mu\text{m}$
Thickness of Silver	2 $\mu\text{m}$

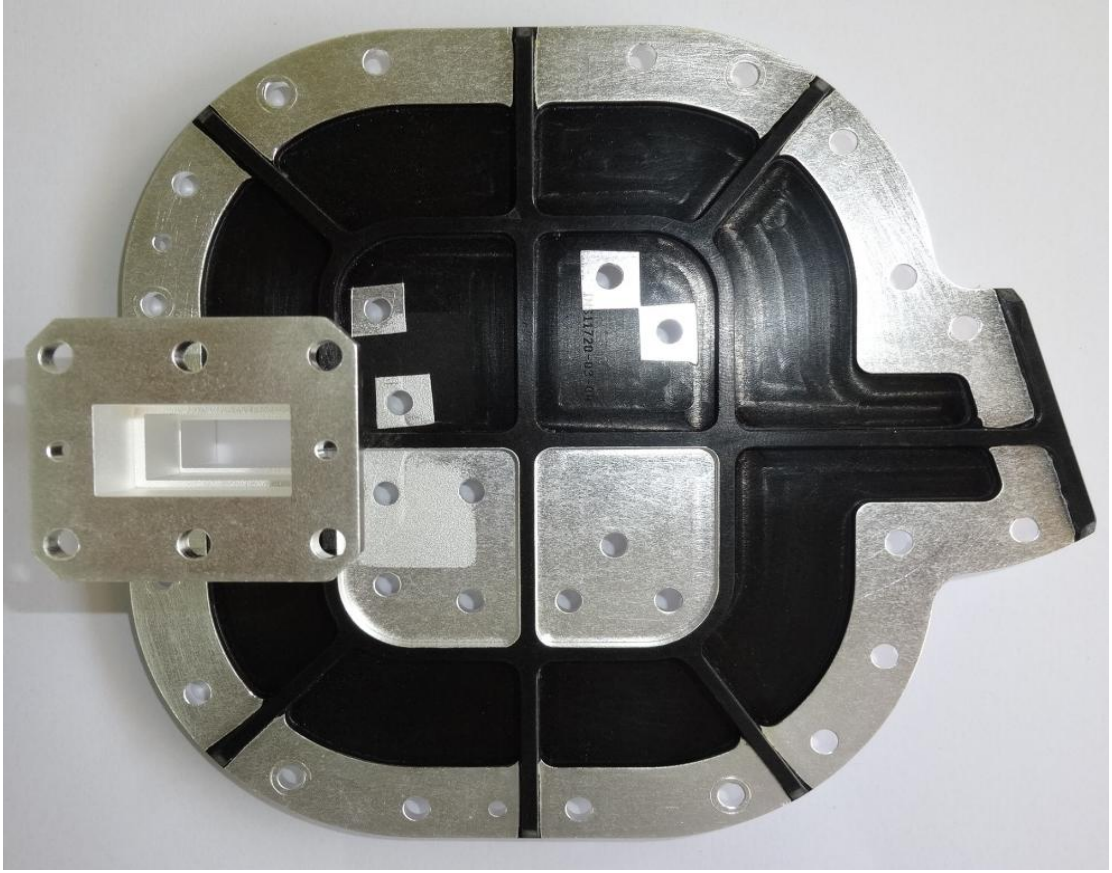
**92. Silver Plating on Kovar Pedestals**

<b>Process UID No</b>	STPD / ST - 17
<b>Brief Description</b>	Developed and qualified the process of Silver Plating on Kovar pedestals as a product qualification to use in GSAT-11 Ku-band 116 MHz DR filters.

**Technical Specifications**

Thickness of Nickel undercoat	3 - 4 $\mu$ m
Thickness of Silver	5 - 8 $\mu$ m

**93. Black Anodizing and Silver Plating on 6061-T6 Aluminum Alloy**

Process UID No	STPD / ST-18
Brief Description	Developed and qualified the process of Black Anodizing and Silver Plating on Aluminum 6061-T6 Alloy for getting good electrical conductivity, solderability inside and high emissivity and high Absorptivity outside various filters and adapters.
	
<b>Technical Specifications</b>	
Thickness of Silver	4-10 $\mu$ m
Thickness of Black Anodizing	22-25 $\mu$ m
Emissivity ( $\epsilon$ )	0.9 $\pm$ 0.02
Solar Absorptivity ( $\alpha$ )	> 0.91



**94. Electroless Nickel Plating on Invar**

Process UID No	STPD / ST-19
Brief Description	Developed and qualified the process of Electroless Nickel Plating on Invar Optical structures, mirror mounts etc., for corrosion protection and good base for thermal control coatings.
	
Technical Specifications	
Thickness of Electroless Nickel Plating	8 - 12µm

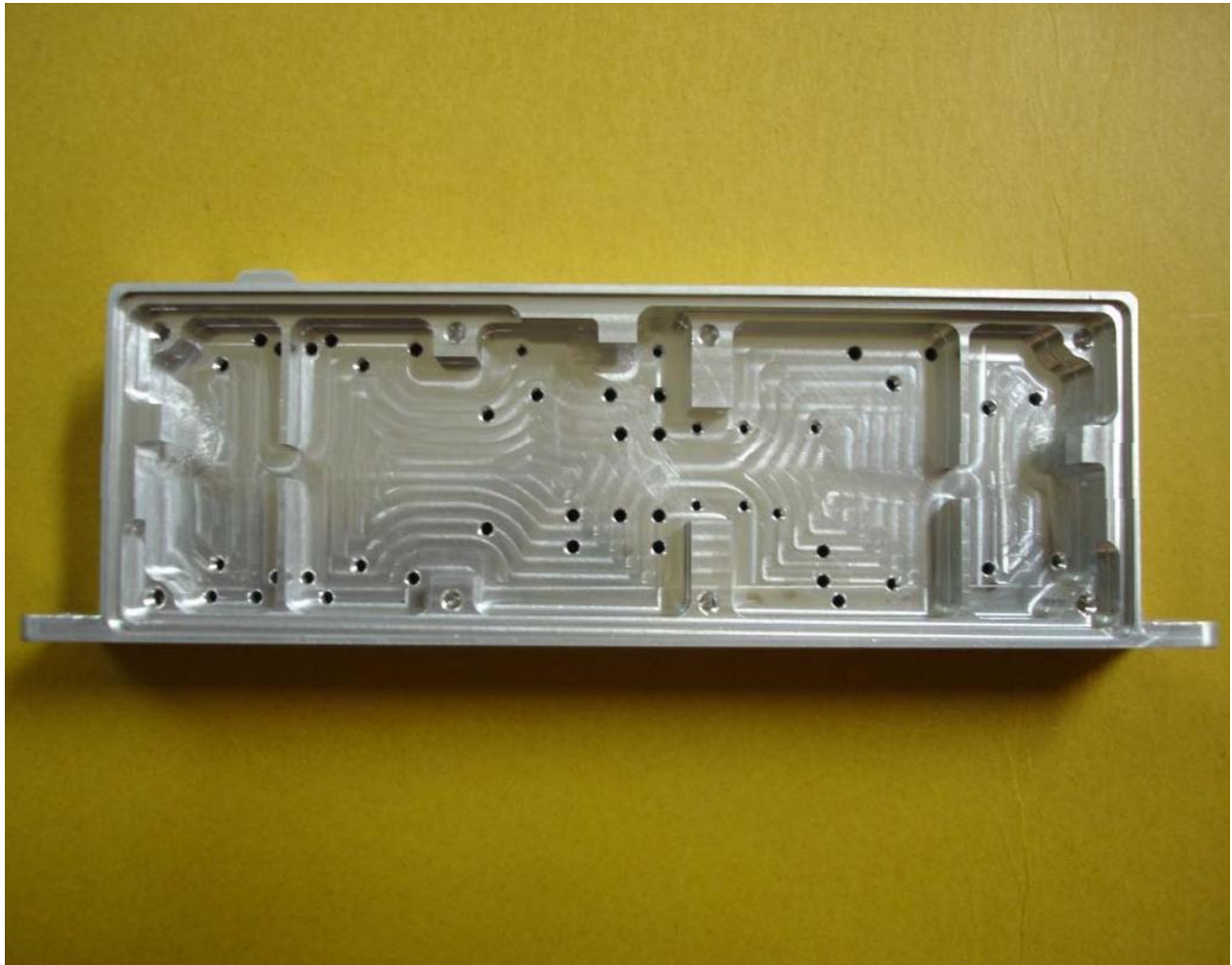


**95. Electroless Nickel Plating on Aluminum 6061-T6 Alloy****Process UID No**

STPD / ST-20

**Brief Description**

Developed and qualified the process of Electroless Nickel Plating on Aluminum boxes and covers for getting corrosion protection and good base for thermal control coatings.

**Technical Specifications**

Thickness of Electroless Nickel Plating

8 - 12 $\mu$ m

**96. Anodizing on Aluminum 6061-T6 Alloy****Process UID No**


STPD / ST-21

**Brief Description**


Developed and qualified the process of Anodizing on Aluminum 6061-T6 Alloy for getting nonconductive surface, corrosion protection, and good base for Thermal Control coatings.

**Technical Specifications****Thickness of Anodizing** $10 \pm 2\mu\text{m}$

**97. Black Anodizing on Aluminum 6061-T6 Alloy**

Process UID No	STPD / ST-22
Brief Description	Developed and qualified the process of Black Anodizing on Aluminum 6061-T6 Alloy packages to achieve high emissivity & solar absorptivity, nonconductive surface, corrosion protection.
	
<b>Technical Specifications</b>	
Thickness of Black Anodizing	25-28 $\mu$
Emissivity ( $\epsilon$ )	0.9 $\pm$ 0.02
Solar Absorptivity ( $\alpha$ )	> 0.91

**98. Black Anodizing by Immersion Process on Aluminum 6061-T6 Alloy**

<b>Process UID No</b>	STPD / ST-23
<b>Brief Description</b>	Developed and qualified an alternative process for black anodizing on Aluminum 6061T6 alloy (to electrolytic black anodizing) which is a 2 solution dip - immersion process.
	
<b>Technical Specifications</b>	
Thickness of Black Anodizing	25µm
Emissivity ( $\epsilon$ )	0.89 - 0.90
Solar Absorptivity ( $\alpha$ )	> 0.88

**99. Chromate conversion coating on Aluminum 6061T6 Alloy**

Process UID No	STPD / ST-24
Brief Description	Developed and qualified the process of Chromate conversion coating on Aluminum 6061T6 alloy for corrosion protection, electrical conductivity and good base for thermal control coatings.
	
Technical Specifications	
Thickness of Chromate Surface	1µm



**100. Chromating & Black Anodizing on Aluminum 6061T6 Alloy**

<b>Process UID No</b>	STPD / ST-25
<b>Brief Description</b>	Developed and qualified the process of Black anodizing and Chromating on Aluminum 6061T6 alloy packages. Black anodizing to achieve high emissivity & solar absorptivity, electrical insulating surface and corrosion protection and Chromating to retain electrical conductivity, corrosion protection and good base for thermal control coatings.
	
<b>Technical Specifications</b>	
Thickness of Chromating	1 $\mu$ m
Thickness of Black Anodizing	25 - 28 $\mu$ m
Emissivity ( $\epsilon$ )	0.9 $\pm$ 0.02
Solar Absorptivity ( $\alpha$ )	$\geq$ 0.91

**101. Chromate conversion coating on Magnesium AZ31B Alloy**

Process UID No	STPD / ST-26
Brief Description	Developed and qualified the process of Chromate conversion coating on Magnesium AZ31B Alloy for corrosion protection, electrical conductivity and good base for thermal control coatings.
	
Technical Specifications	
Thickness of chromate surface	1 $\mu$

**102. Black Anodizing on Magnesium Alloy AZ-31B**

<b>Process UID No</b>	STPD / ST - 27
<b>Brief Description</b>	Developed and qualified the process of Black Anodizing on Magnesium Alloy AZ31B Alloy packages to achieve high emissivity & solar absorptivity, nonconductive surface, corrosion protection.

**Technical Specifications**

Thickness of Black Anodizing	4-7 $\mu$ m
Emissivity ( $\epsilon$ )	0.75 $\pm$ 0.05
Solar Absorptivity ( $\alpha$ )	0.8

**103. Galvanic Anodizing on Magnesium Alloy AZ-31B**

<b>Process UID No</b>	STPD / ST - 28
<b>Brief Description</b>	Developed and qualified the process of Galvanic Anodizing on Magnesium Alloy AZ31B Alloy packages to achieve high emissivity & solar absorptivity, nonconductive surface, corrosion protection.
	
<b>Technical Specifications</b>	
Thickness of Black Anodizing	3-5 $\mu$ m
Emissivity ( $\epsilon$ )	0.72 - 0.79
Solar Absorptivity ( $\alpha$ )	0.83 - 0.88

**104. Black Anodizing and Chromate conversion coating on Magnesium Alloy AZ-31B**

<b>Process UID No</b>	STPD / ST- 29
<b>Brief Description</b>	Developed and qualified the process of Black Anodizing and Chromate conversion coating on Magnesium Alloy AZ-31B, for getting nonconductive surface, Optical properties like emissivity and absorptivity, corrosion resistance and good base for paint for subsystem components of various satellites.

**Technical Specifications**

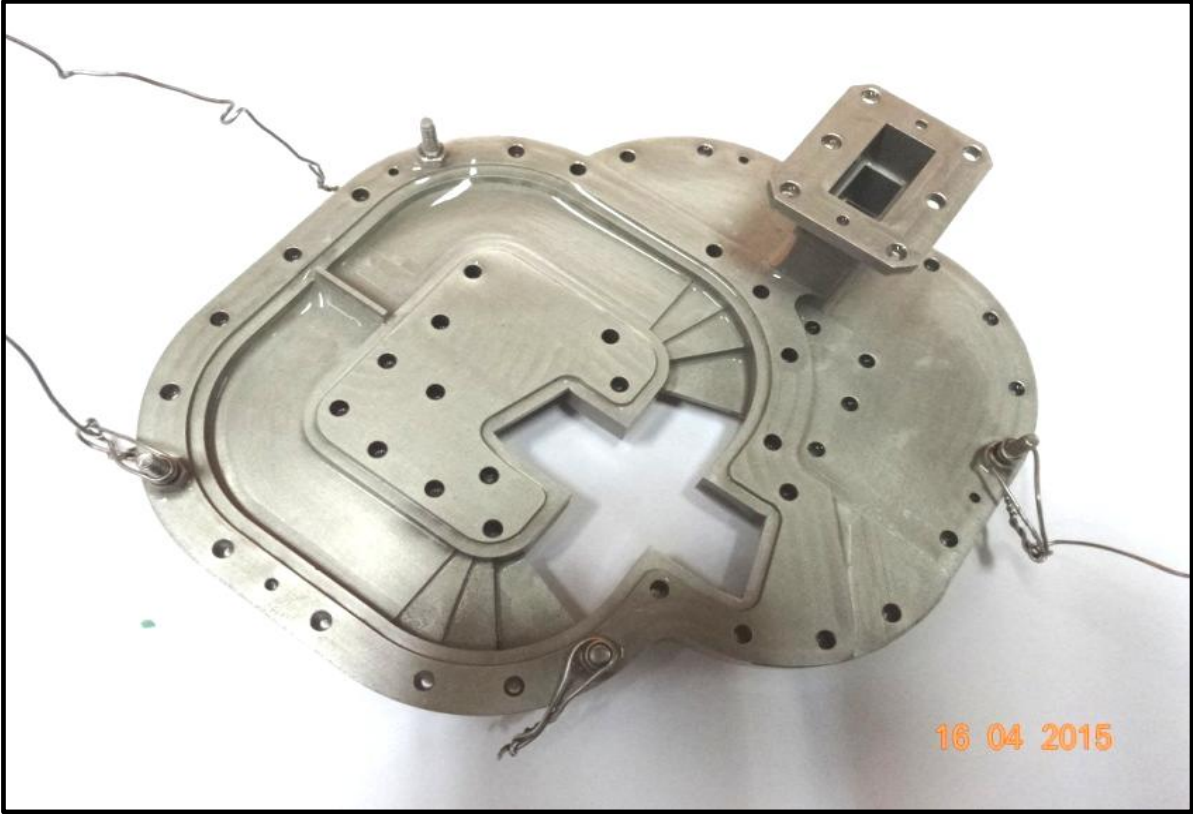
Thickness of Black Anodizing	4-7 $\mu$ m
Emissivity ( $\epsilon$ )	0.75 $\pm$ 0.05
Solar Absorptivity ( $\alpha$ )	0.8
Thickness of chromate surface	1-2 $\mu$ m



**105. Black Nickel Plating on Invar**

<b>Process UID No</b>	STPD / ST- 30
<b>Brief Description</b>	Developed and qualified the process of Black Nickel on Invar to achieve optical properties suitable for electro-optical payloads.
	
<b>Technical Specifications</b>	
Thickness of Black Nickel Plating	10 - 15 $\mu\text{m}$
Emissivity ( $\epsilon$ )	$\geq 0.71$
Solar Absorptivity ( $\alpha$ )	$\geq 0.90$

**106. Electroless Nickel Plating on Magnesium AZ31B Alloy**

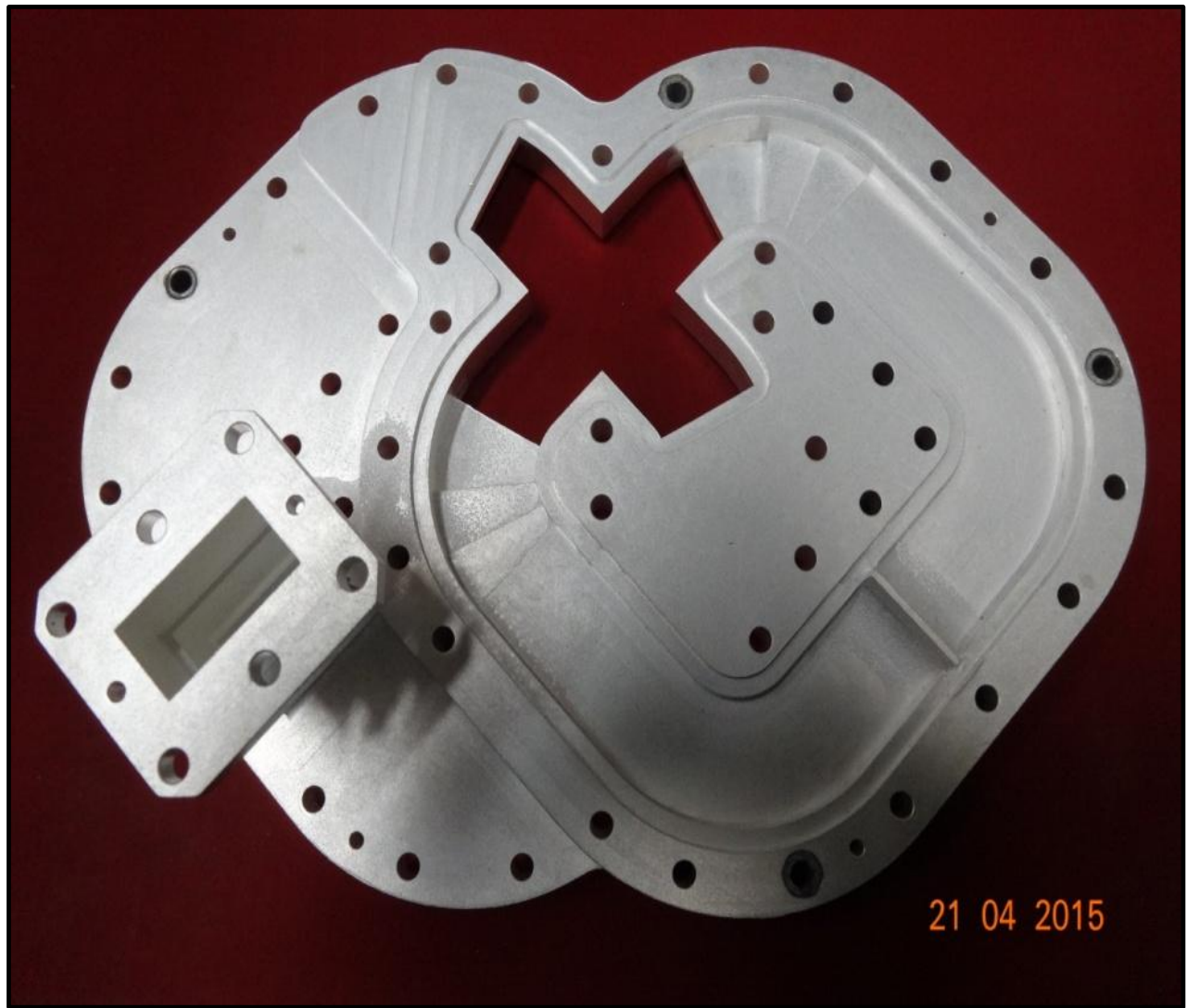
Process UID No	STPD / ST- 31
Brief Description	Developed and qualified the process of Electroless nickel plating on Magnesium AZ31B alloy boxes and covers for corrosion resistance and good base for thermal control coatings.
	
Technical Specifications	
Thickness of Black Nickel Plating	8 - 12 $\mu\text{m}$

**107. Silver Plating on Magnesium AZ31B Alloy****Process UID No**

STPD / ST- 32

**Brief Description**

Developed and qualified the process of Silver plating on Magnesium AZ31B Alloy components like UHF, OMT cavity, filters for electrical conductivity & solderability, corrosion resistance and good base for thermal control coatings.

**Technical Specifications****Thickness of Silver Plating**4 - 6  $\mu\text{m}$

**108. Fluoride Treatment on Magnesium AZ31B Alloy**

<b>Process UID No</b>	STPD / ST- 33
<b>Brief Description</b>	Developed and qualified the process of Fluoride treatment on Magnesium AZ31B Alloy packages to achieve high emissivity & solar absorptivity, non conductive surface, corrosion protection, and good base for thermal control coatings.

**Technical Specifications**

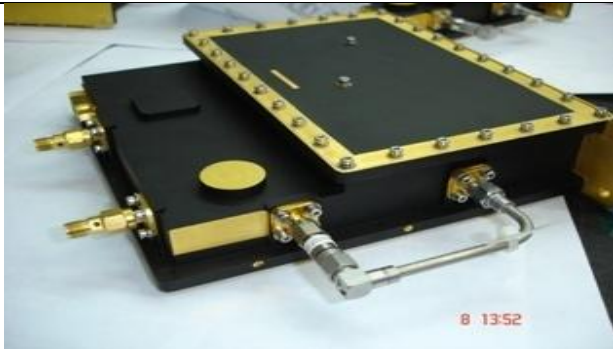
Thickness of Black Nickel Plating	4 - 6 $\mu\text{m}$
Emissivity ( $\epsilon$ )	$\geq 0.75$
Solar Absorptivity ( $\alpha$ )	$\geq 0.90$
Salt Spray Resistance	$\geq 24$ Hrs

**109. Black Nickel Plating on Magnesium AZ31B Alloy**

Process UID No	STPD / ST- 34
Brief Description	Developed and qualified the process of Black nickel plating on Magnesium packages and covers for getting good electrical conductivity, solderability, optical properties, corrosion protection and good base for thermal control coatings.
	
<b>Technical Specifications</b>	
Thickness of Black Nickel Plating	18 - 20 $\mu\text{m}$
Emissivity ( $\epsilon$ )	$\geq 0.85$
Solar Absorptivity ( $\alpha$ )	$\geq 0.92$
Salt Spray Resistance	$\geq 24$ Hrs



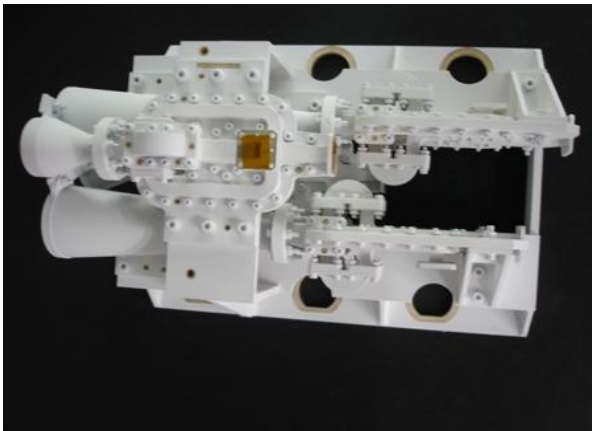
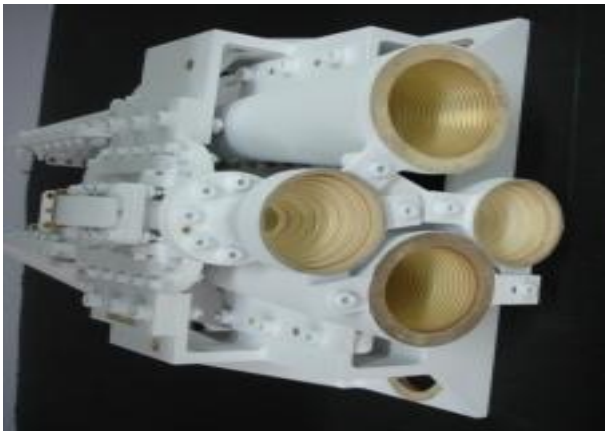
**110. Black Thermal Control Coating for High Emissivity & Solar Absorptivity**

<b>Process UID No</b>	STPD / TP - 01	
<b>Brief Description</b>	Developed and qualified the process of Black Thermal Control coating with high emissivity and solar absorptivity to facilitate radiant heat transfer among internal components of satellites. This process is qualified on following different base substrates:-	
<ul style="list-style-type: none"> <li>➤ Anodized Aluminum 6061T6 alloy</li> <li>➤ Chromated Aluminum 6061T6 alloy</li> <li>➤ Aluminum 6061T6 alloy</li> <li>➤ Electroless Nickel Plated Al 6061T6</li> <li>➤ Silver plated Aluminum 6061T6 alloy</li> <li>➤ Gold plated Aluminum 6061T6 alloy</li> <li>➤ Aluminum 2024 alloy</li> </ul>	<ul style="list-style-type: none"> <li>➤ Silver plated Aluminum 2024 alloy</li> <li>➤ Invar</li> <li>➤ Electroless Nickel plated Invar</li> <li>➤ Silver plated Invar</li> <li>➤ Magnesium AZ31B alloy</li> <li>➤ Black Anodized Magnesium AZ31B alloy</li> <li>➤ Chromated Magnesium AZ31B alloy</li> </ul>	
		
<b>Technical Specifications</b>		
Dry Film Thickness	50-75 $\mu\text{m}$	
Appearance & Colour	Flat Black	
Emissivity ( $\epsilon$ )	>0.90	
Solar Absorptivity ( $\alpha$ )	> 0.94	
Surface Resistance	$\geq 10^{10}$ ohm/square	
Total Mass Loss (TML)	$\leq 1.00\%$	
Collected Volatile Condensable Material (CVCM)	$\leq 0.10\%$	
Curing Time to Use	$\geq 7$ days	
Vacuum Baking for Optical Components	65 °C/24 hours/ $10^{-5}$ torr (or) 50 °C/48hours/ $10^{-5}$ torr	

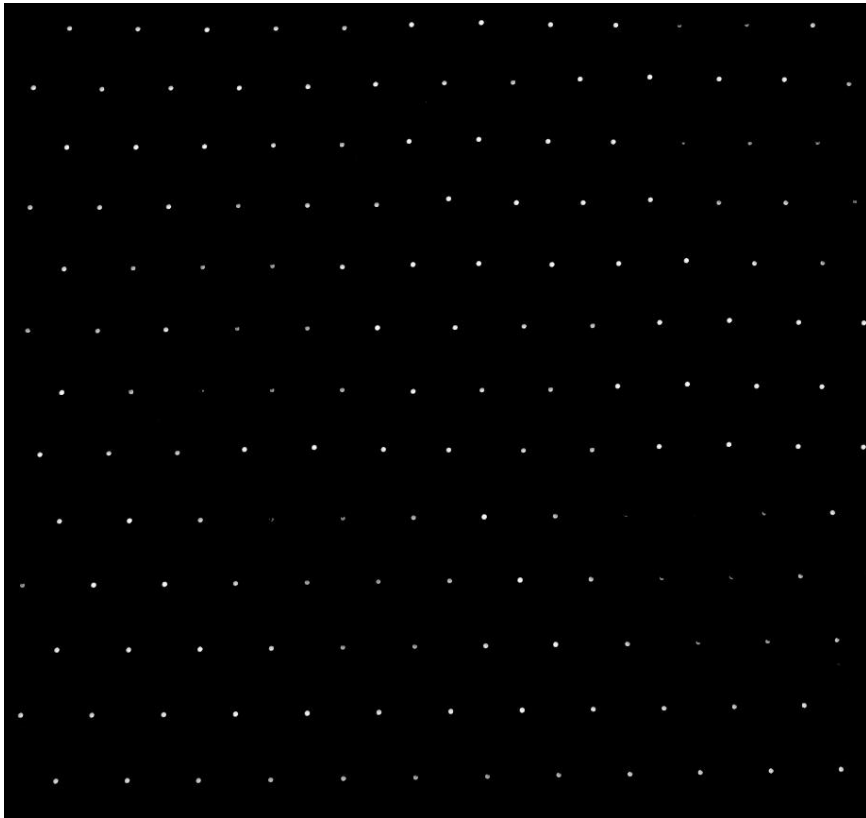
**111. Black Thermal Control Coating for High Temperature Applications**

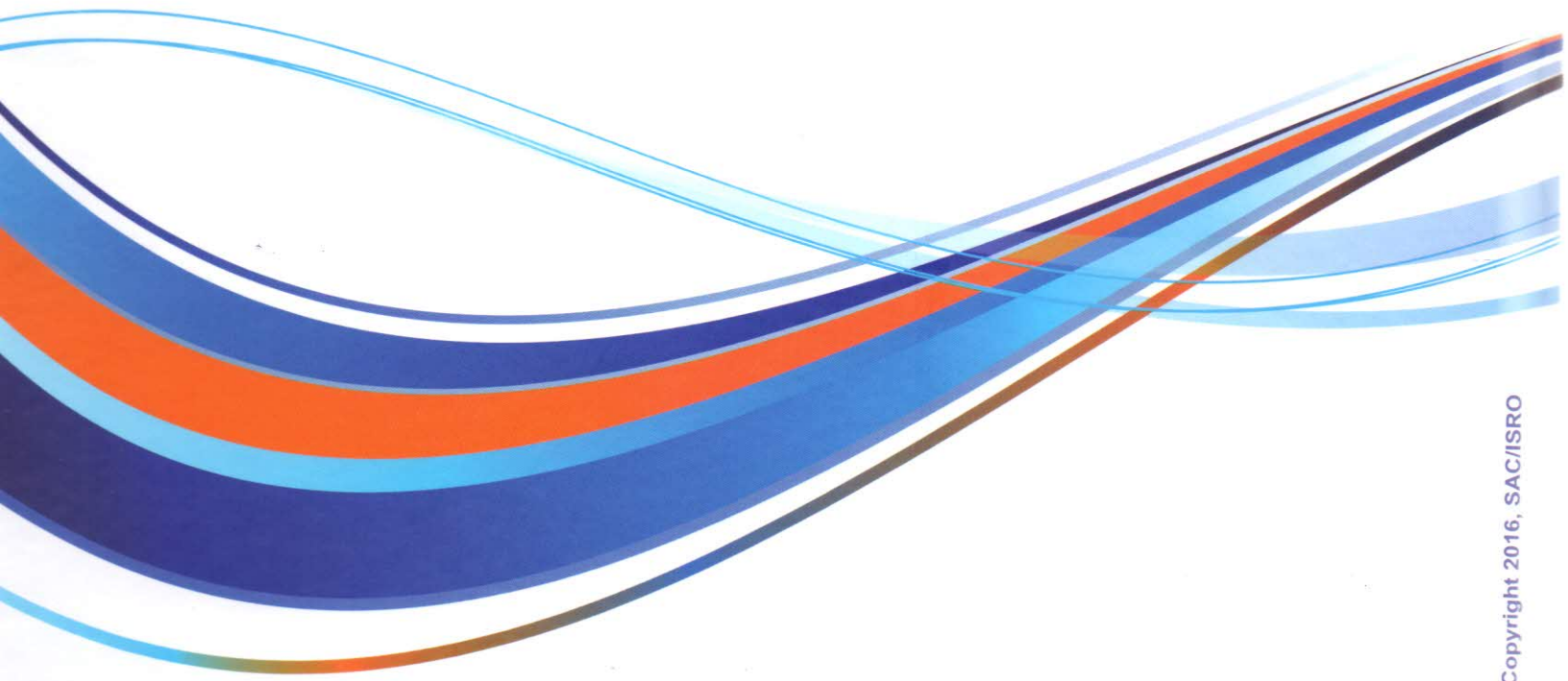
Process UID No	STPD / TP - 02		
Brief Description	<p>Developed and qualified the process of Black Thermal Control coating for High Temperature applications with high emissivity and solar absorptivity to facilitate radiant heat transfer.</p> <p>This process is qualified on Anodized Aluminum 6061T6 alloy.</p>		
			
Technical Specifications			
Dry Film Thickness		80-110 μ	
Appearance &Colour		Matt Black	
Emissivity (ε)		≥ 0.90	
Solar Absorptivity (α)		≥ 0.94	
Temperature Range		up to 250 °C	
Surface Resistance		≥ 10 <sup>10</sup> ohm/square	
Total Mass Loss (TML)		≤ 1.00%	
Collected Volatile Condensable Material (CVCM)		≤ 0.10%	
Curing Time to Use		7 days	
Vacuum Baking for Optical Components		65 °C/24 hours/10 <sup>-5</sup> torr      (or) 50 °C/48hours/10 <sup>-5</sup> torr	

**112. White Thermal Control Coating for High Temperature Applications**

Process UID No	STPD / TP - 03	
Brief Description	<p>Developed and qualified the process of White Thermal Control coating for high temperature applications with high emissivity and high reflectivity for components exposed to direct solar radiation.</p> <p>This process is qualified on Silver plated Aluminum Alloy 6061T6 alloy.</p>	
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Technical Specifications		
Dry Film Thickness	100-130 μm	
Appearance & Colour	Flat White	
Emissivity (ε)	≥ 0.88	
Solar Absorptivity (α)	≥ 0.20	
Temperature Range	Up to 250 °C	
Surface Resistance	≥ 10 <sup>10</sup> ohm/square	
Total Mass Loss (TML)	≤ 1.00%	
Collected Volatile Condensable Material (CVCM)	≤ 0.10%	
Curing Time to Use	7 days	
Vacuum Baking for Optical Components	65 °C / 24 hours / 10 <sup>-5</sup> torr (or) 50 °C / 48hours / 10 <sup>-5</sup> torr	

**113. Black Thermal Control Coating on Kapton Tape**

Process UID No.	STPD / TP - 04		
Brief Description	Developed and qualified the process of Black Thermal Control coating on Kapton Tape with adhesive transfer sheet.		
			
Technical Specifications			
Dry Film Thickness		35-50 μm	
Appearance & Colour		Flat Black	
Emissivity (ε)		>0.90	
Solar Absorptivity (α)		> 0.94	
Total Mass Loss (TML)		≤ 1.00%	
Collected Volatile Condensable Material (CVCM)		≤ 0.10%	
Curing Time to Use		7 days	



**Contact**

**Technology Transfer and Industry Interface Division  
Planning and Projects Group  
Space Applications Centre, ISRO  
Ambawadi Vistar, Ahmedabad-380015.  
Web: [www.sac.gov.in](http://www.sac.gov.in)  
Email: [ttid@sac.isro.gov.in](mailto:ttid@sac.isro.gov.in)  
Fax : +91-79-26915817**